

DANAE

A new effort to directly search for Dark Matter with DEPFET-RNDR detectors

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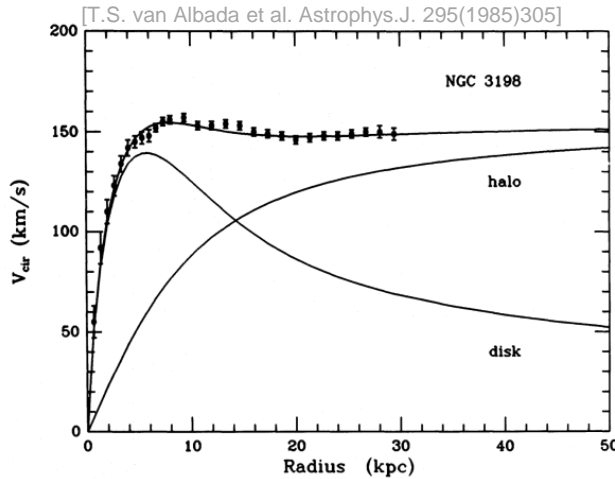
² Atominstitut, Technische Universität Wien, Austria

³ Max-Planck-Gesellschaft Halbleiterlabor, Germany

Outline

- Sub-GeV/c² dark matter:
why is it attractive
- DEPFET-RNDR detectors:
how do they work
- The DANAЕ project:
its current status
- Physics perspective:
what we aim for

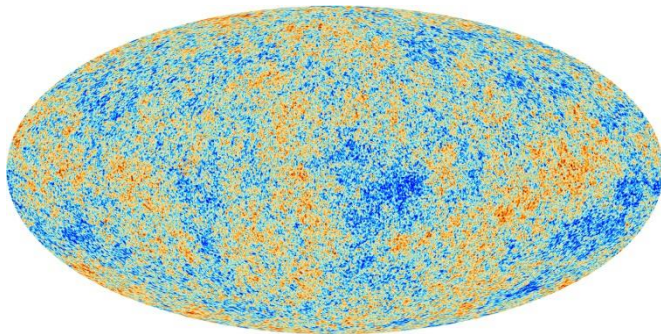
Sub-GeV/c² dark matter



Several astronomical evidences for the existence of dark matter at different scales



[NASA/CXC/SAO]



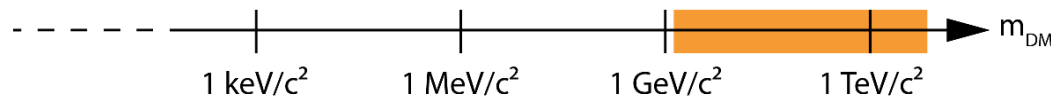
[ESA and the Planck Collaboration]

Cosmic Microwave Background + Big Bang Nucleosynthesis

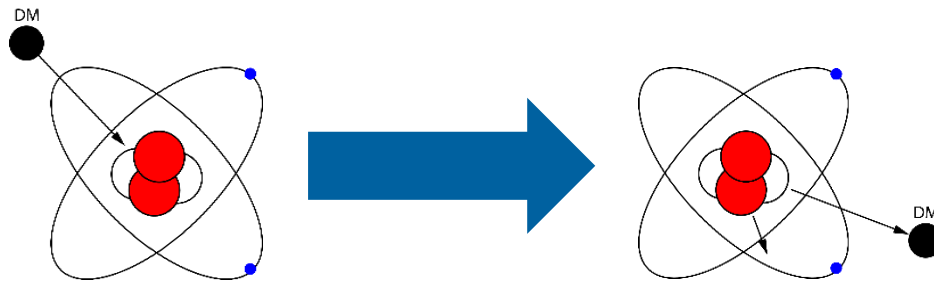
→ **~20%** of Universe is Dark Matter but no unambiguous particle candidate

WIMP dark matter

- **WIMP** is a classic particle candidate for DM
- Predicted particle mass $2\text{GeV}/c^2 \dots 120\text{TeV}/c^2$

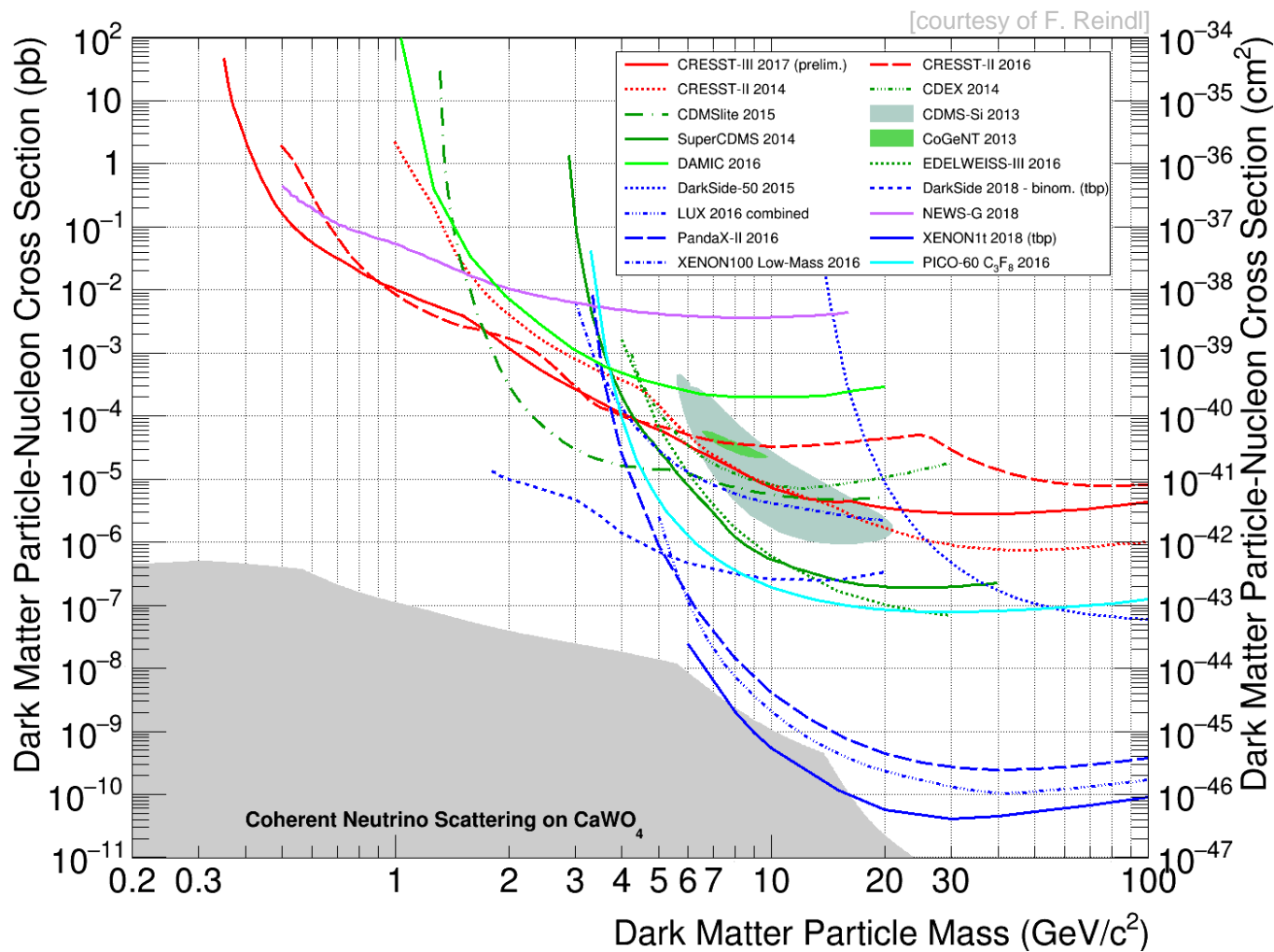


- Usual event signature in direct searches: nuclear recoils

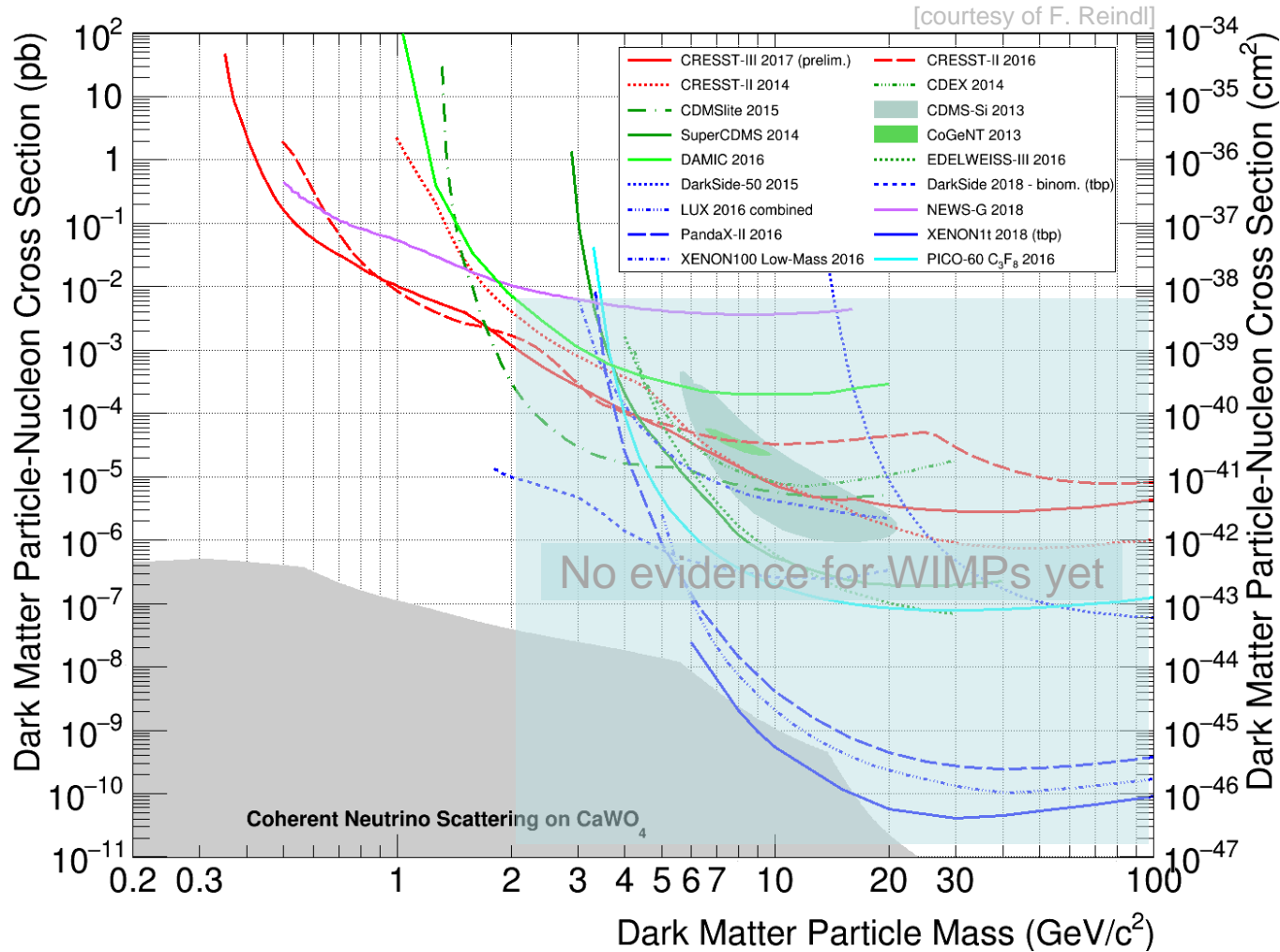


- Dominated the direct searches until recently

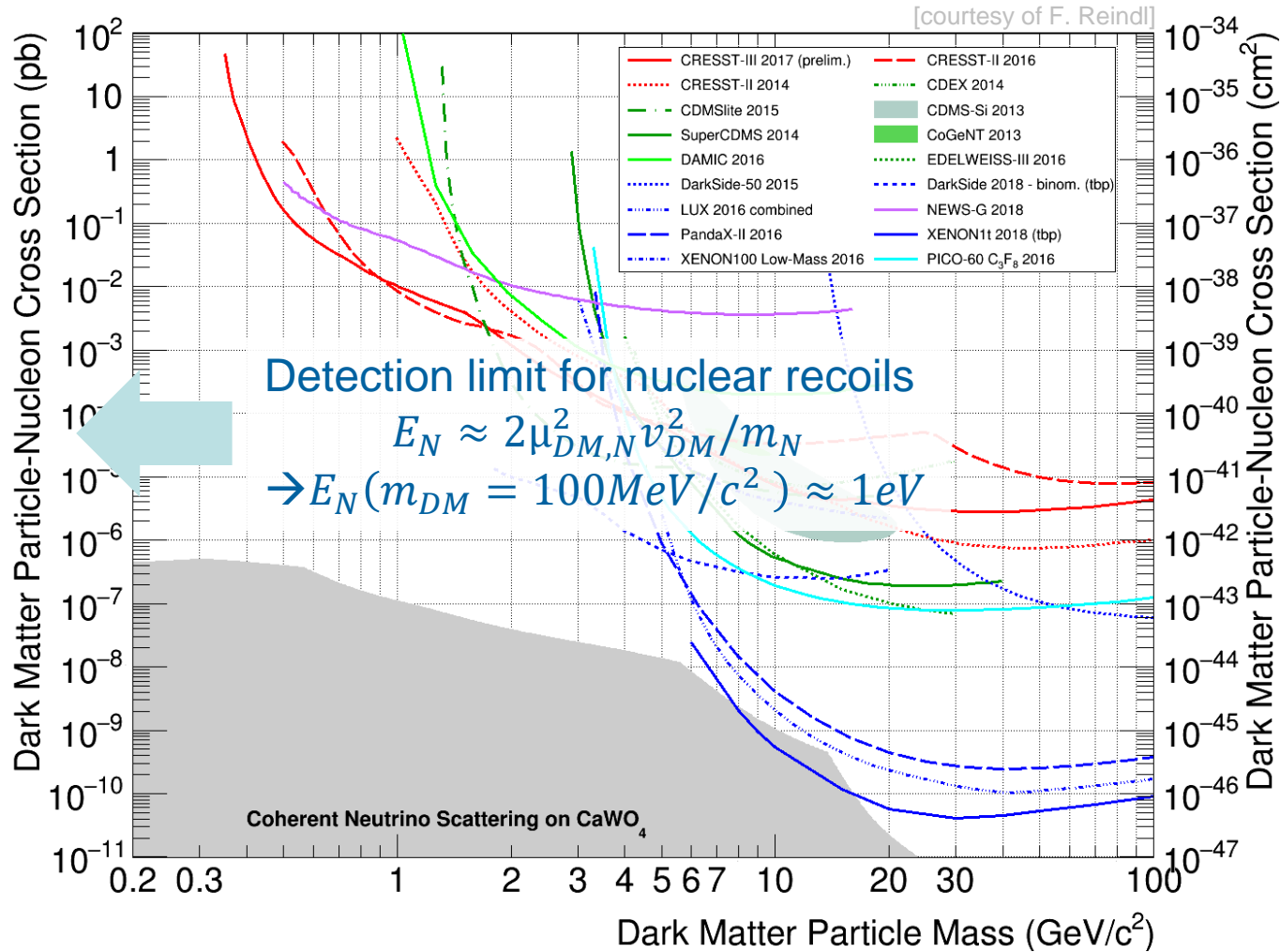
Landscape



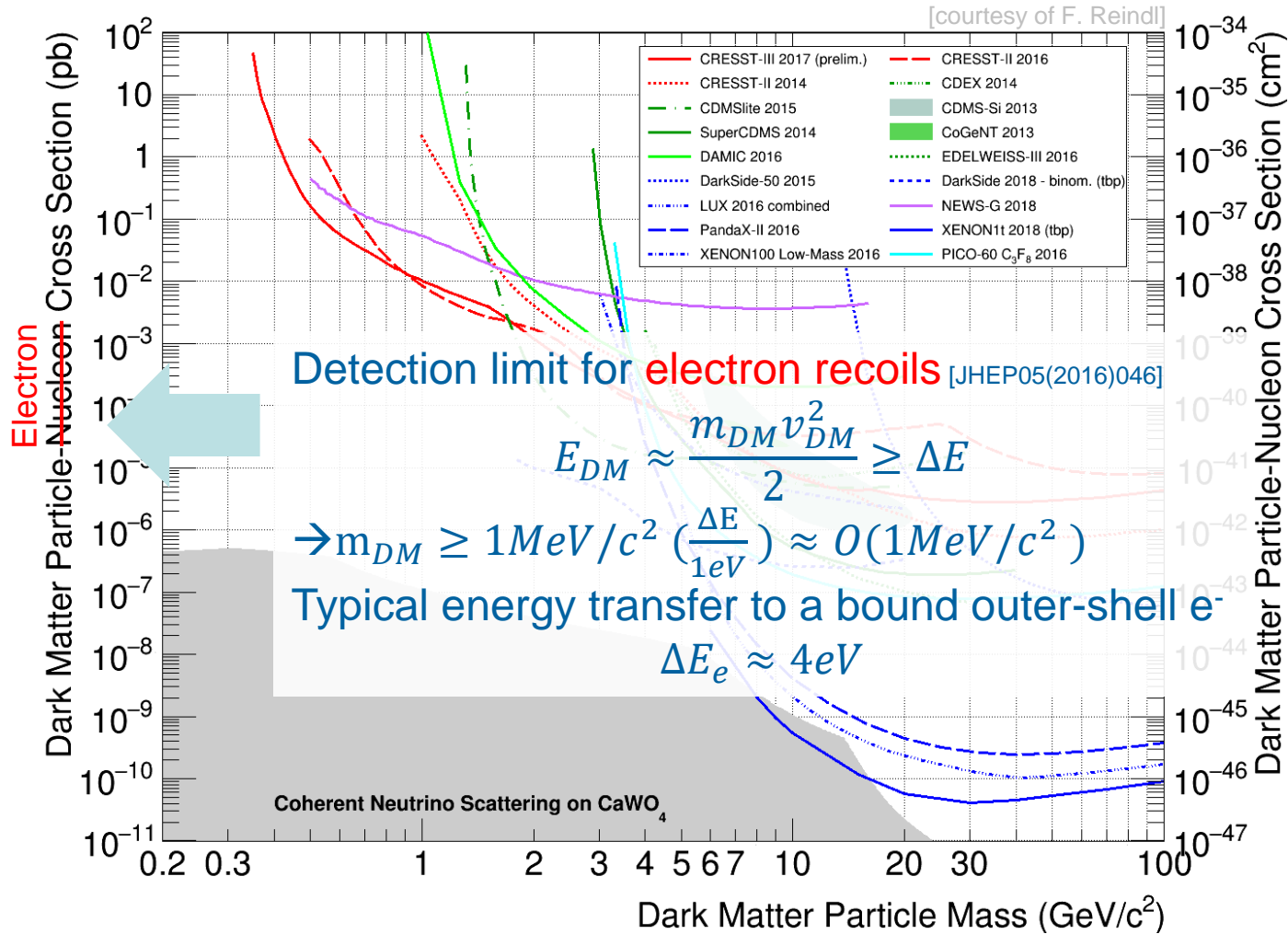
Landscape



Landscape

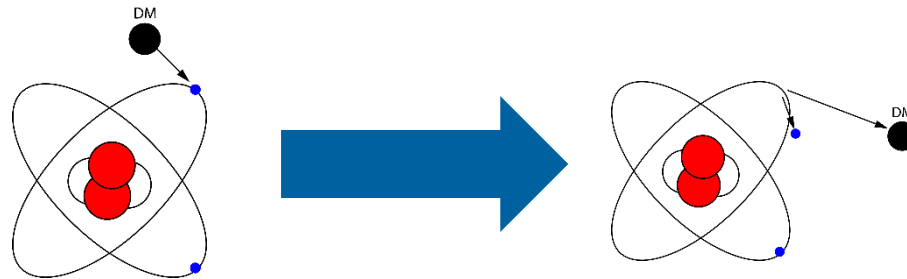


Landscape

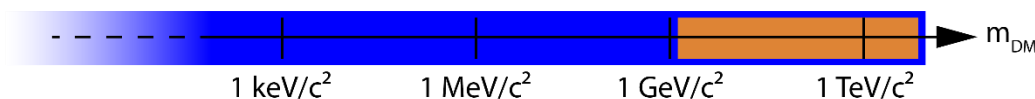


Dark sector and light dark matter

- **Dark sector:** interaction between DM and SM mediated by new particle(s), e.g. dark photons
- Possible event signature in direct searches: electron scattering



- Mass prediction from several models (e.g. freeze-out, asymmetric DM, freeze-in, SIMP, ELDER) including keV/c^2 to GeV/c^2 scale



Target materials for e^- scattering

Active target	Detection threshold	DM mass threshold	Status	Time scale
Noble liquids (e.g. Xe, Ar, Ne)	~ 10 eV	~ 5 MeV/ c^2	Done with data; improvements possible	existing
Semiconductors (e.g. Ge, Si)	~ 1 eV	~ 200 keV/ c^2	($E_{th} \sim 40$ eV SuperCDMS, DAMIC) $E_{th} \sim 1$ eV SENSEI, DANAÉ R&D	~ 1 -2 yr
Scintillators (e.g. CsI, NaI, ...)	~ 1 eV	~ 200 keV/ c^2	R&D required	$\lesssim 5$ yr
Superfluid (e.g. He)	~ 1 eV	~ 1 MeV/ c^2	R&D required unknown background	$\lesssim 5$ yr
Superconductor (e.g. Al)	~ 1 meV	~ 1 keV/ c^2	R&D required unknown background	~ 10 -15 yr

[arXiv:1608.08632]

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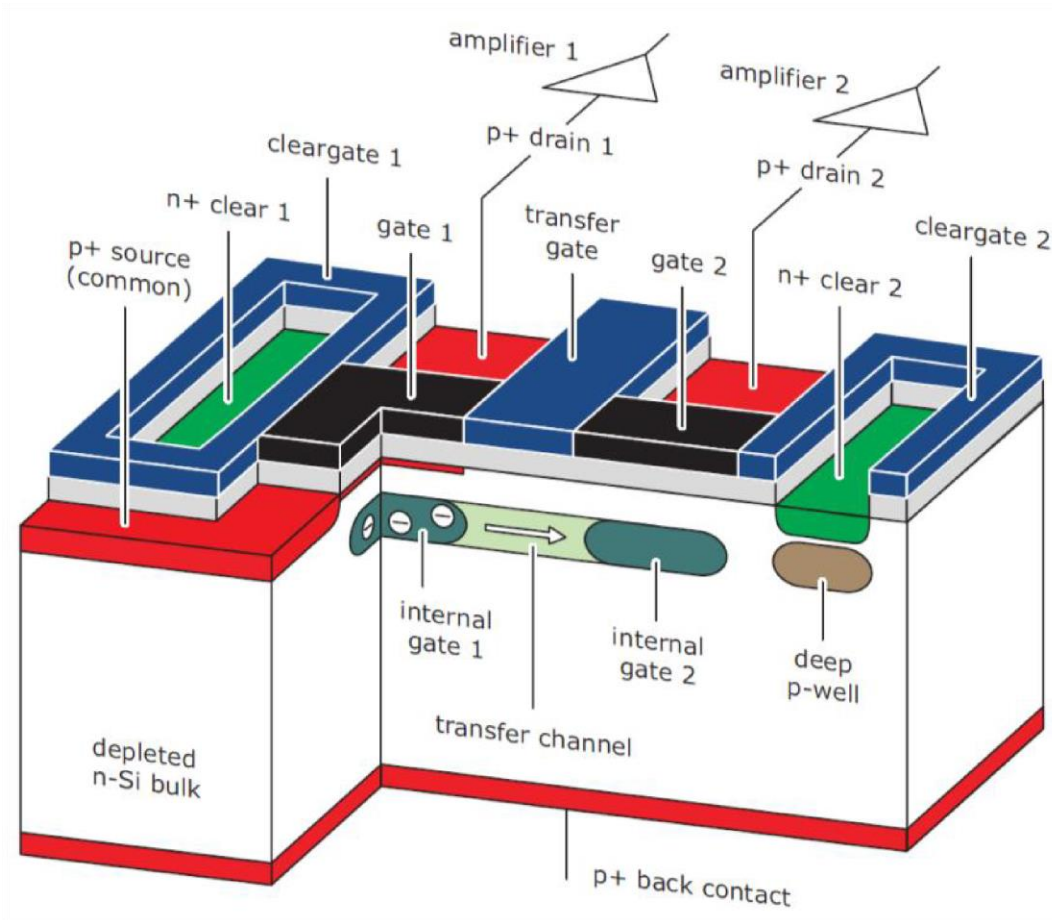
Single DM- e^- interactions:
 $\rightarrow < 1e^-$ RMS noise level

[arXiv:1608.08632]

DEPFET-RNDR detectors

DEPFET-RNDR

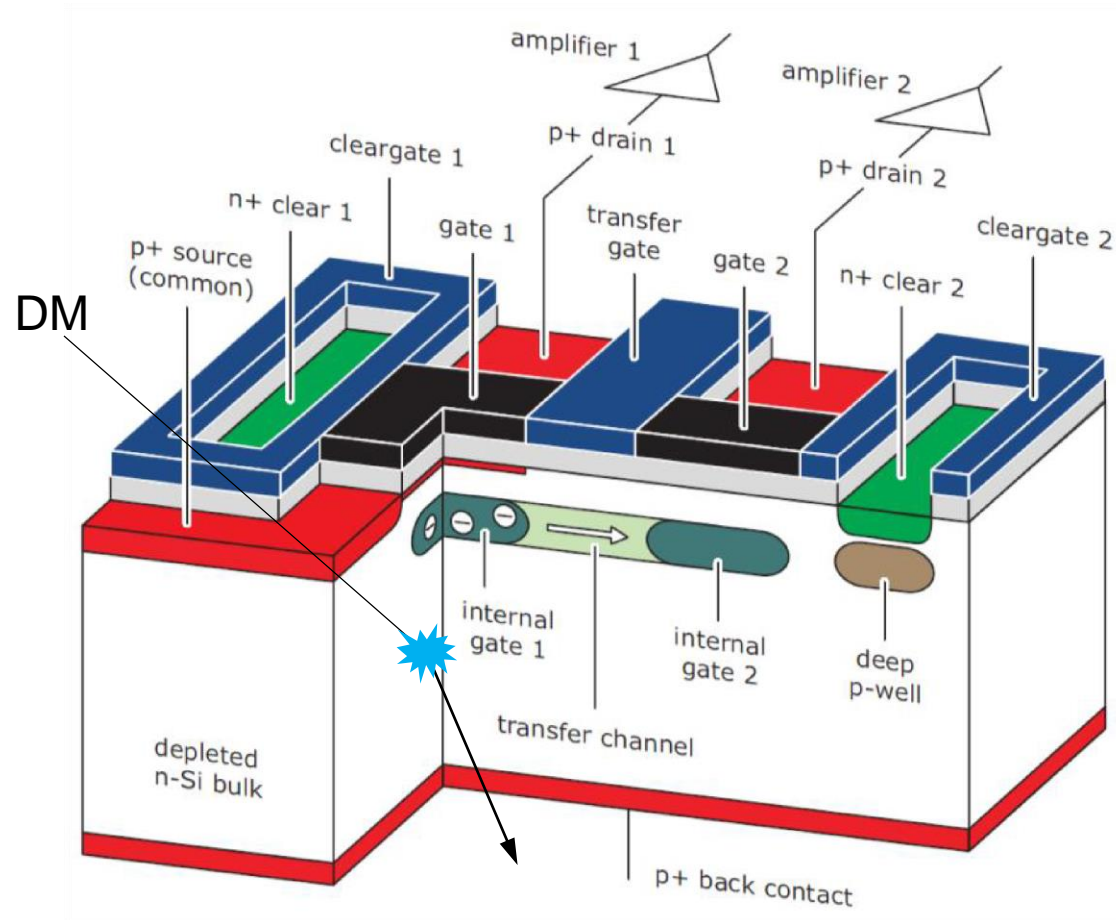
Depleted P-channel Field Effect Transistor with Repetitive Non Destructive Readout



DEPFET-RNDR „super-pixel“ [Eur. Phys. J. C77.12(2017)279]

DEPFET-RNDR

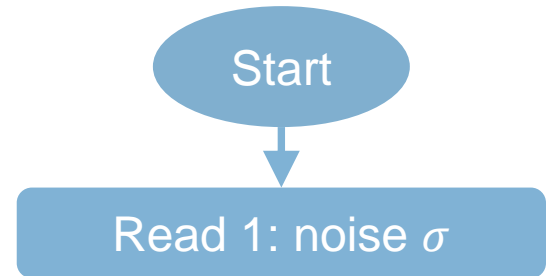
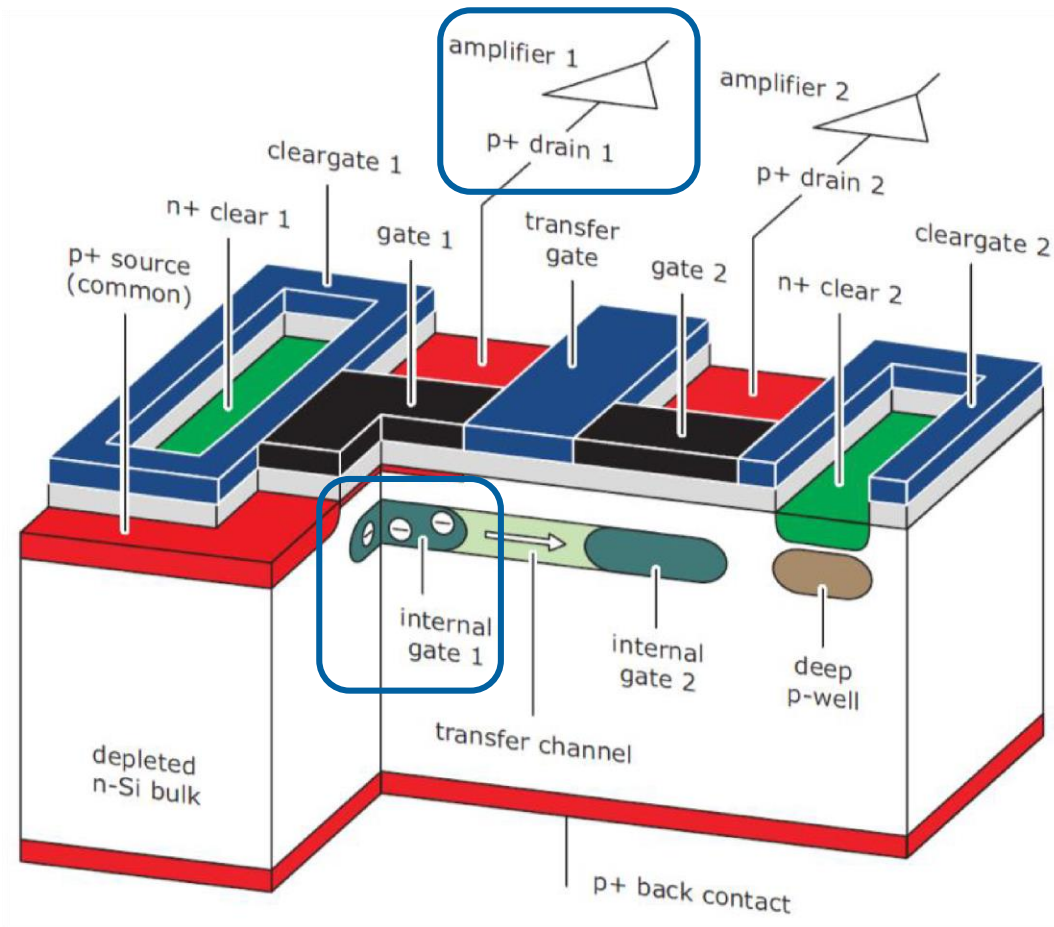
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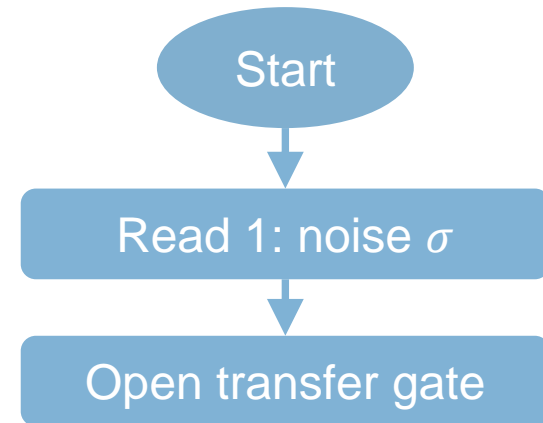
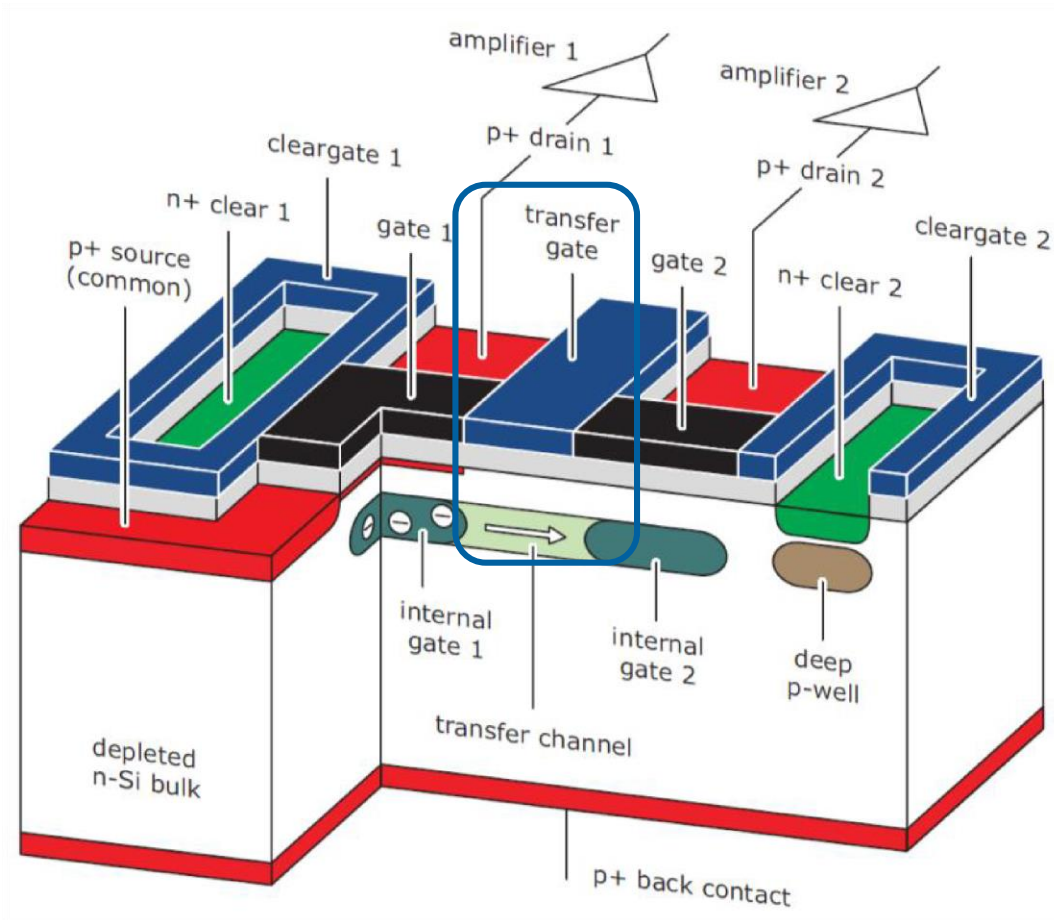
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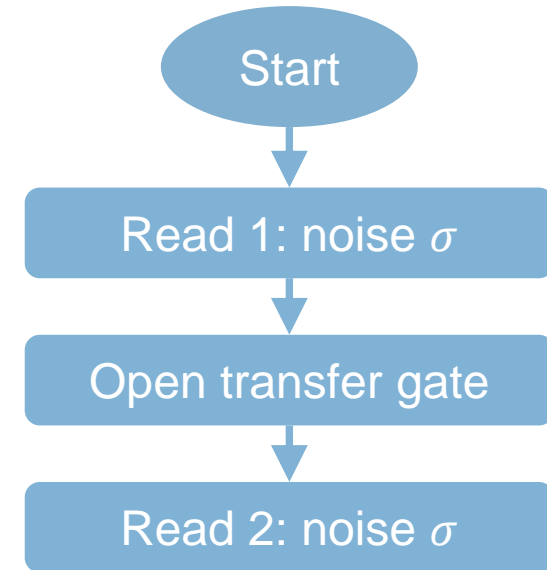
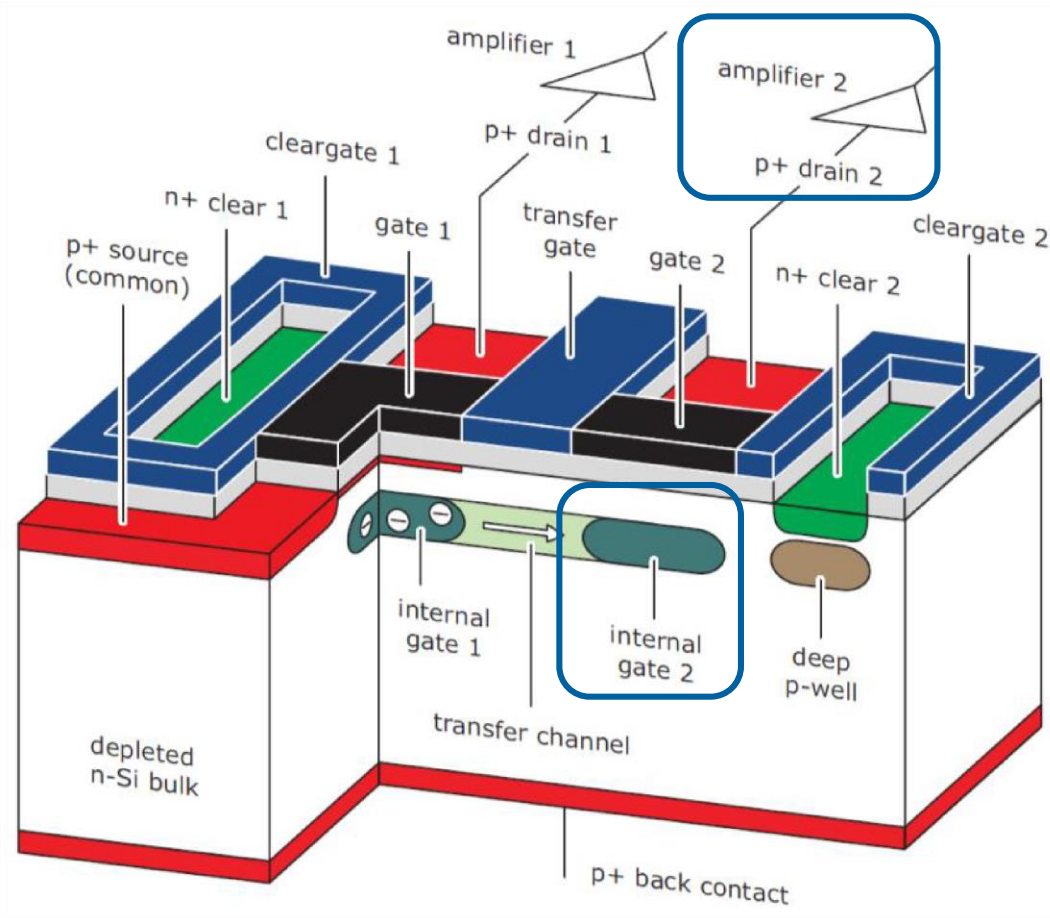
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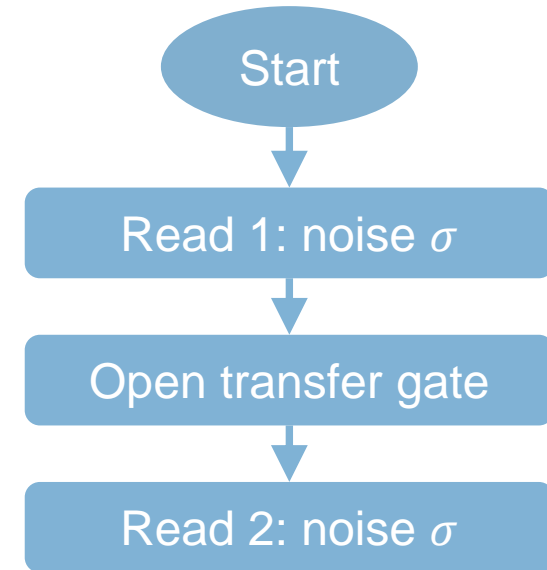
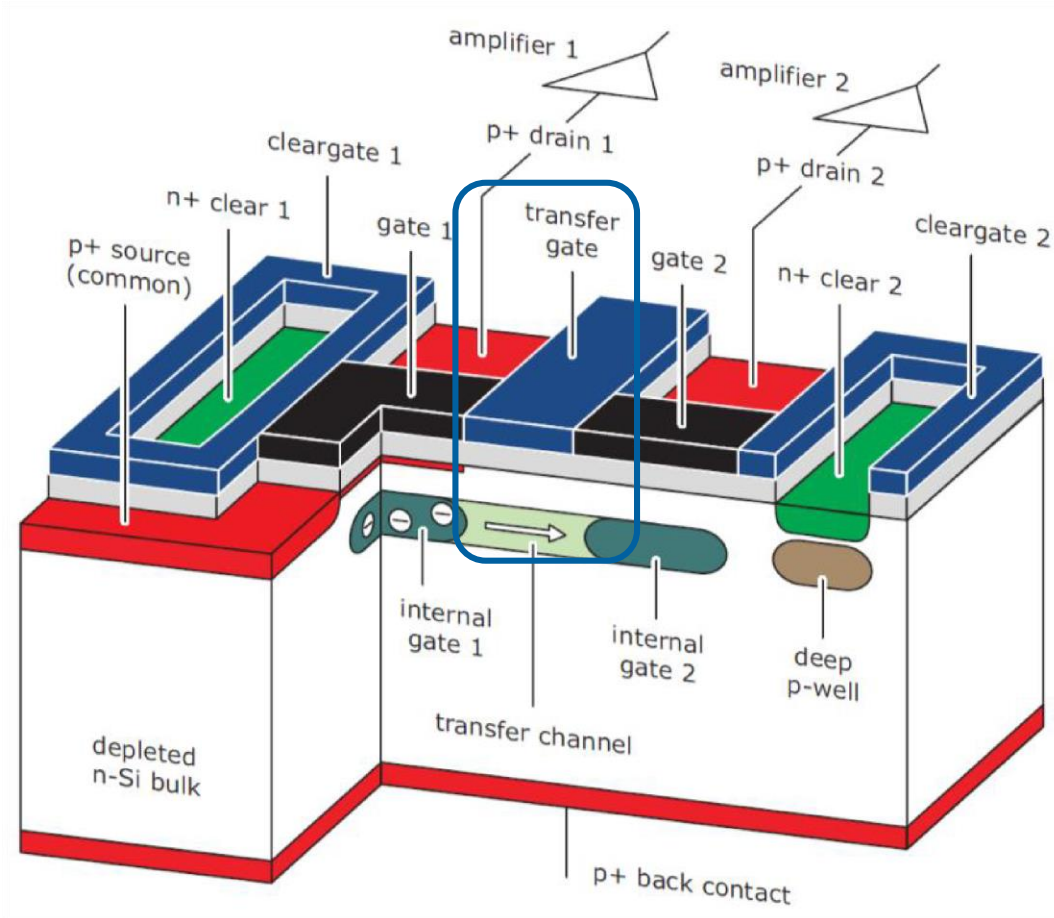
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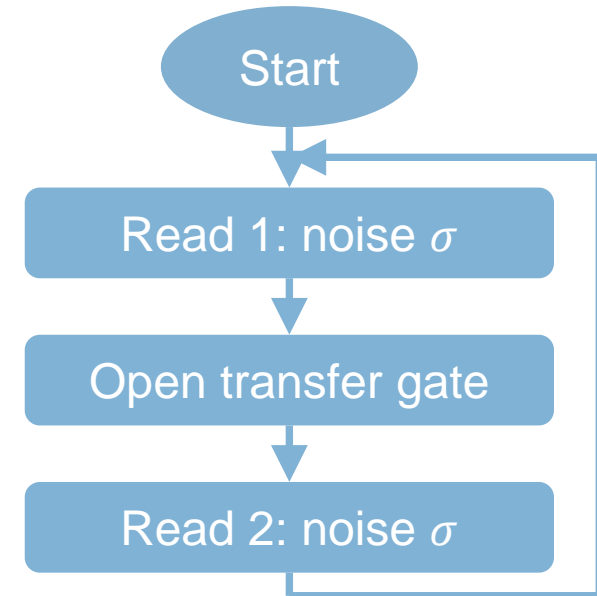
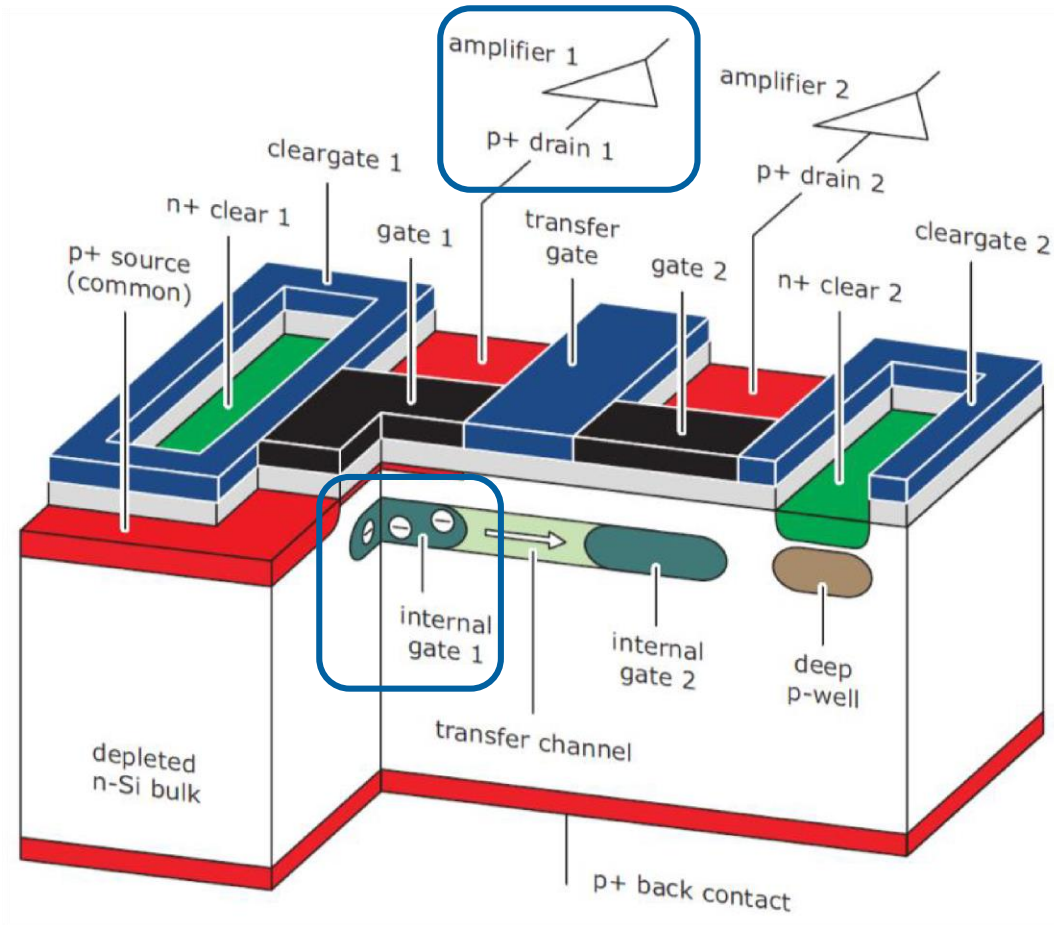
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DEPFET-RNDR

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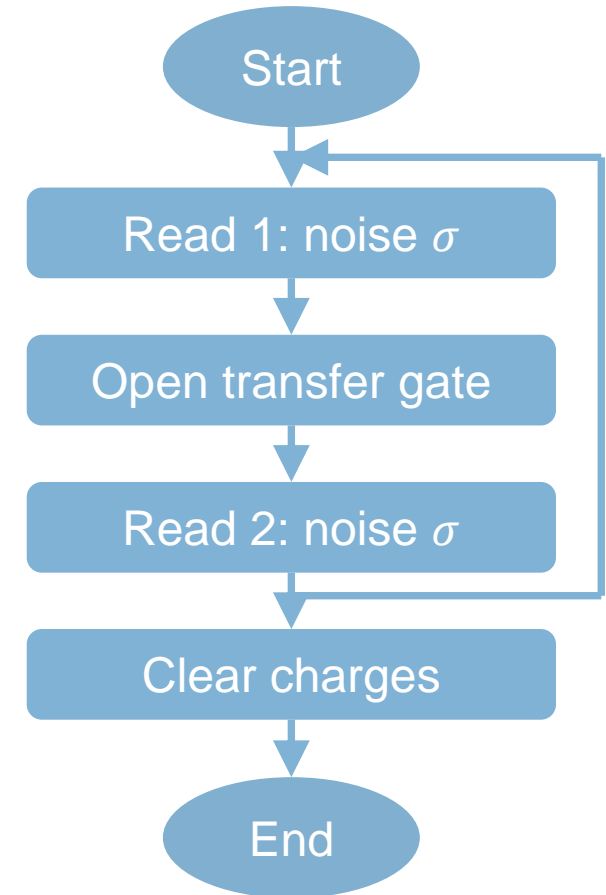
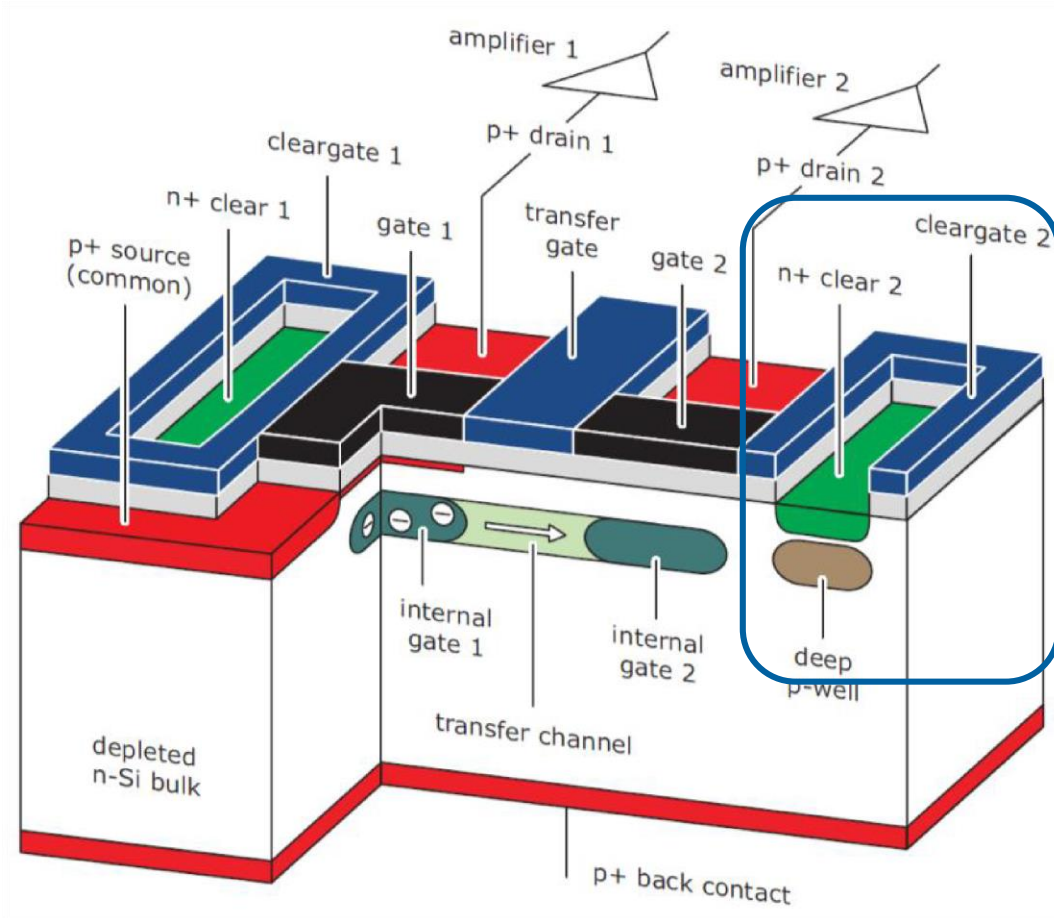


Repeat: N independent measurements with CDS

DEPFET-RNDR „super-pixel“ [Eur. Phys. J. C77.12(2017)279]

DEPFET-RNDR

Depleted P-channel Field Effect Transistor with Repetitive Non Destructive Readout



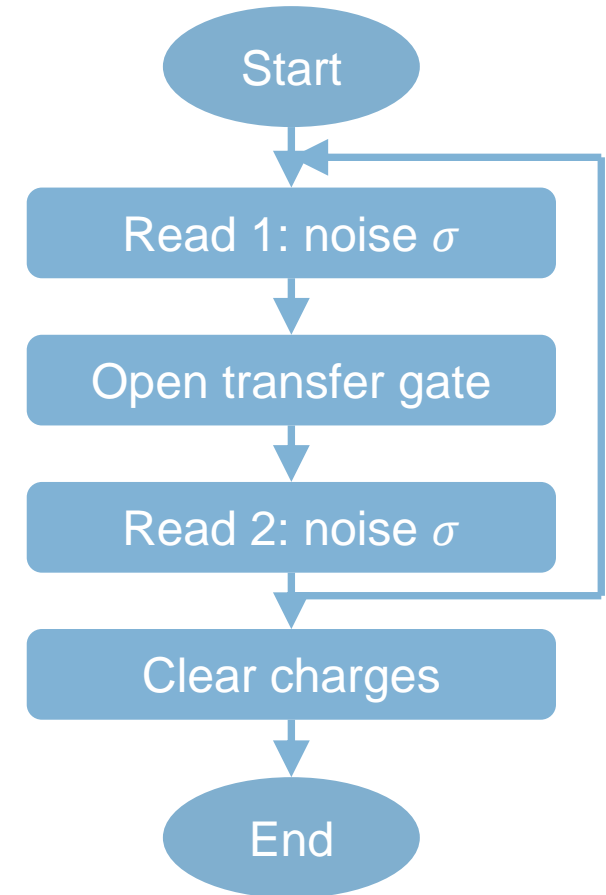
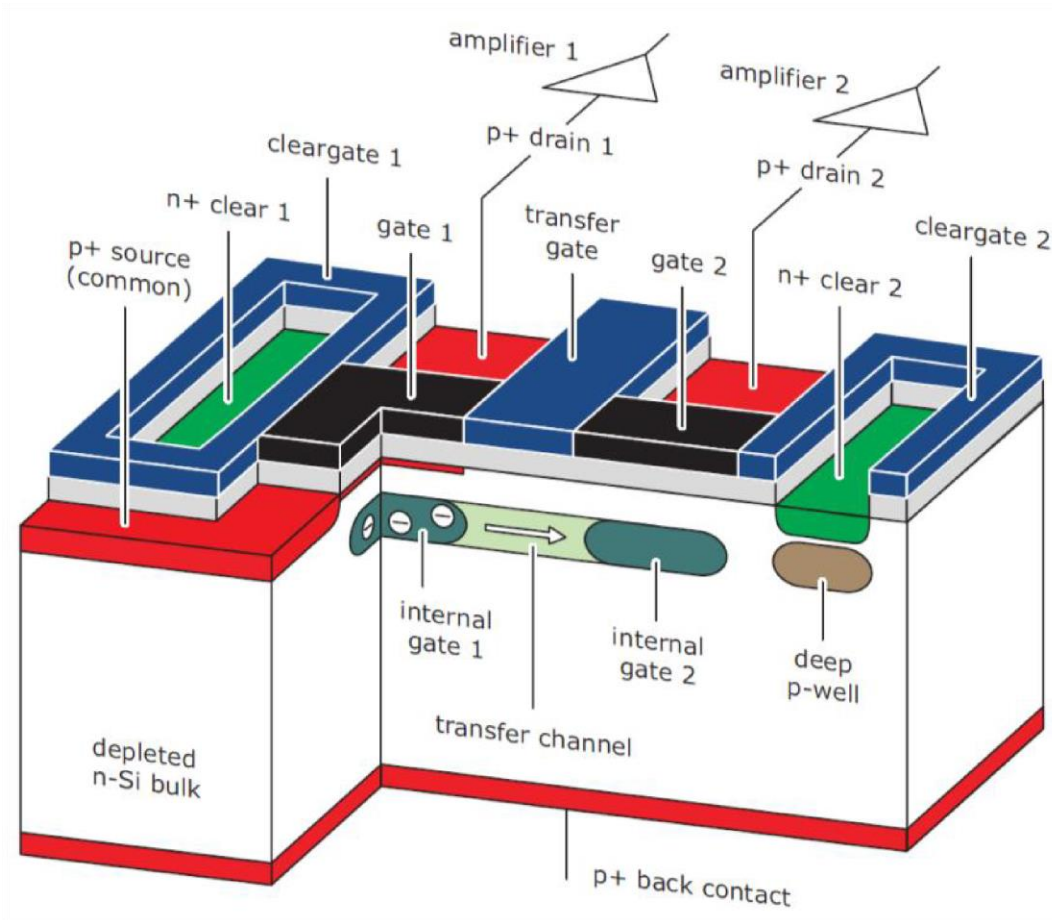
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DEPFET-RNDR „super-pixel“ [Eur. Phys. J. C77.12(2017)279]

Effective noise: $\sigma_{eff} = \sigma/\sqrt{N}$

DEPFET-RNDR

Depleted P-channel Field Effect Transistor with Repetitive Non Destructive Readout

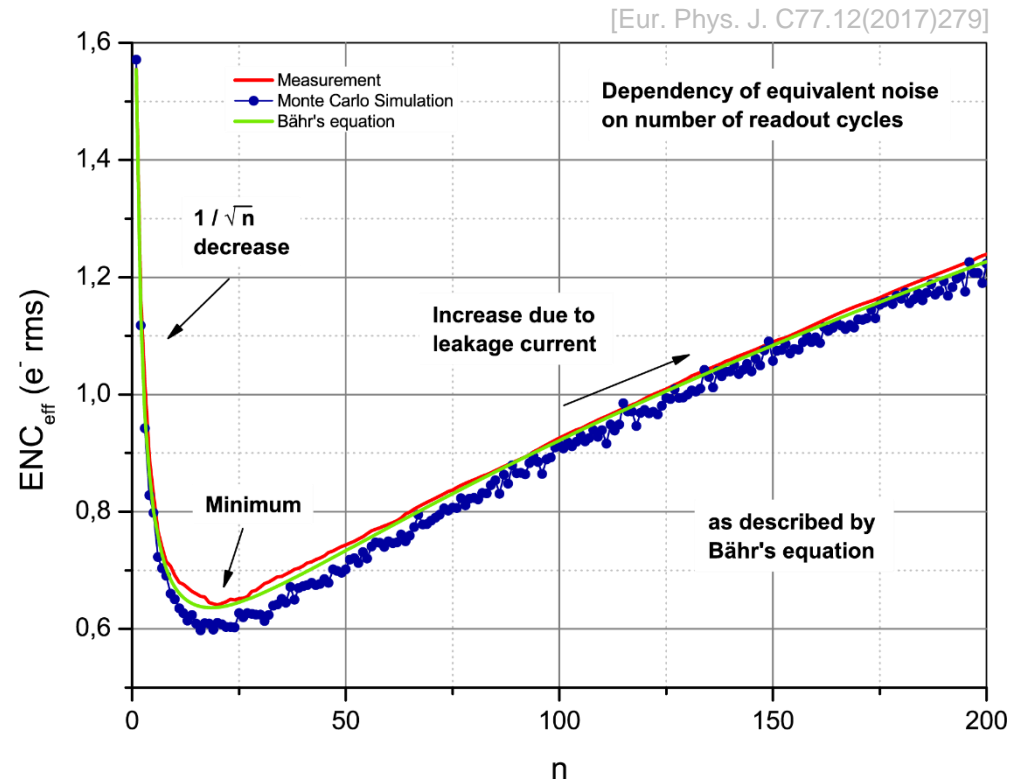


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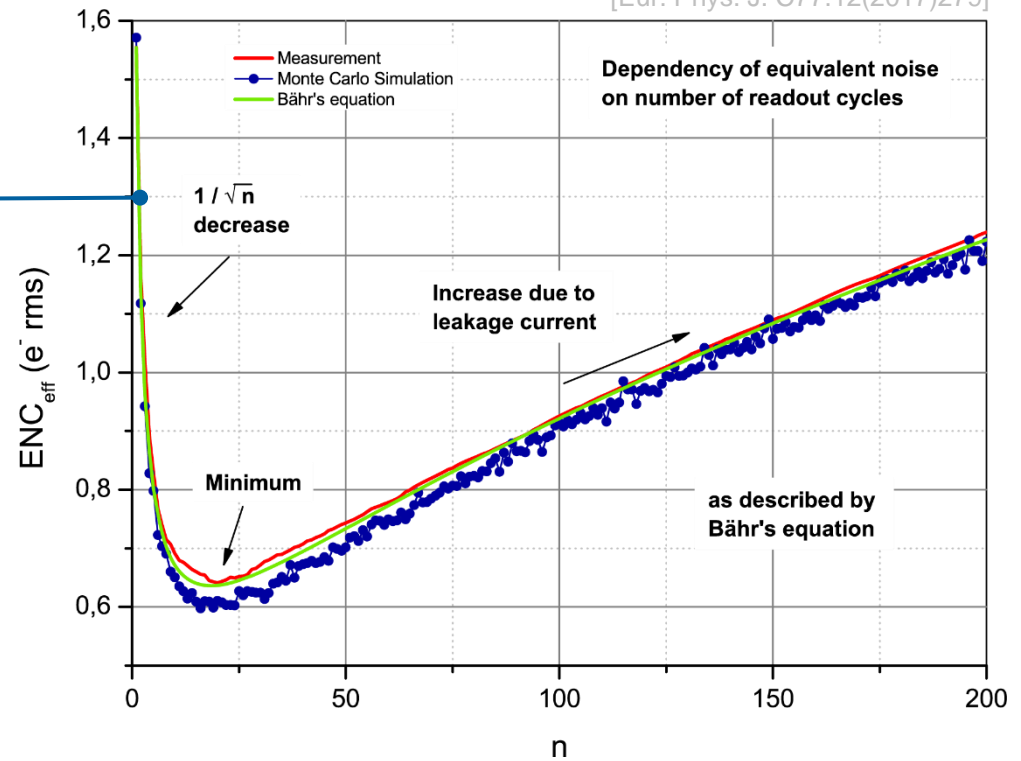
DEPFET-RNDR single pixel performance



DEPFET-RNDR single pixel performance

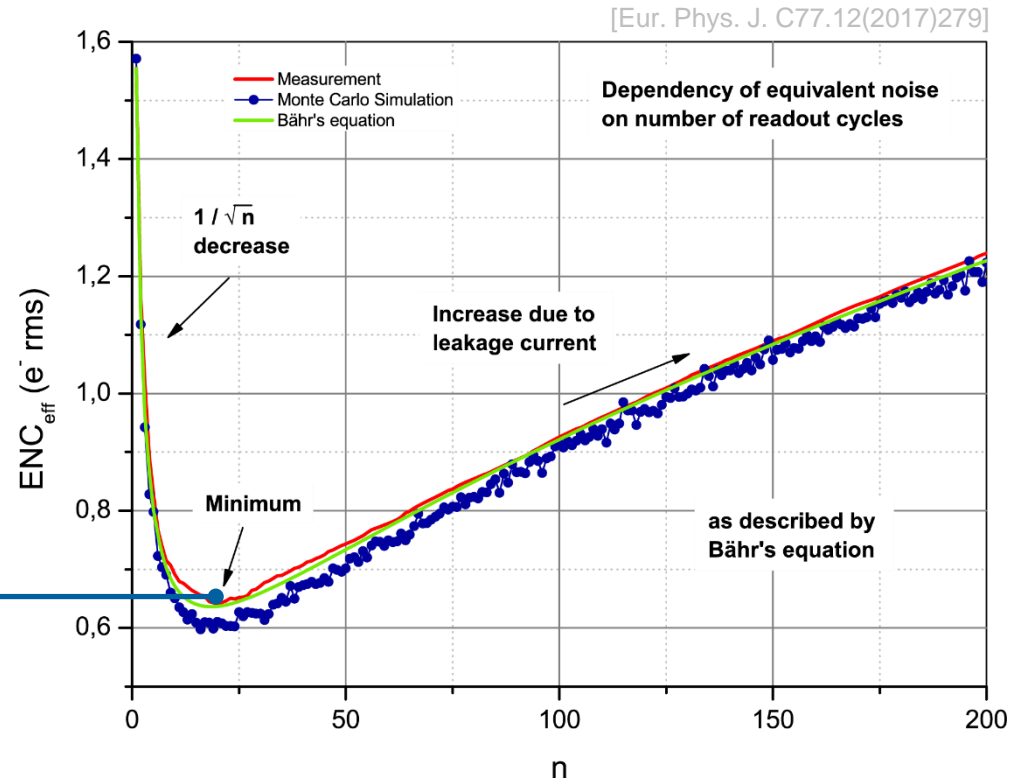
[Eur. Phys. J. C77.12(2017)279]

$\sigma_{eff} \sim 1/\sqrt{N}$ confirmed

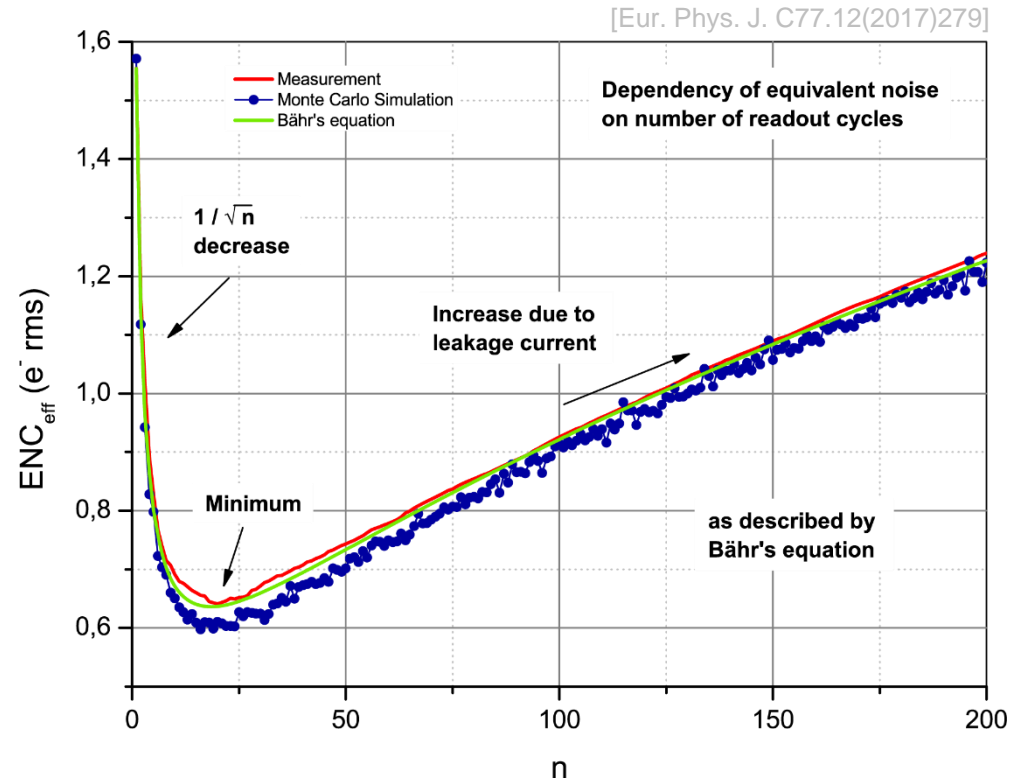
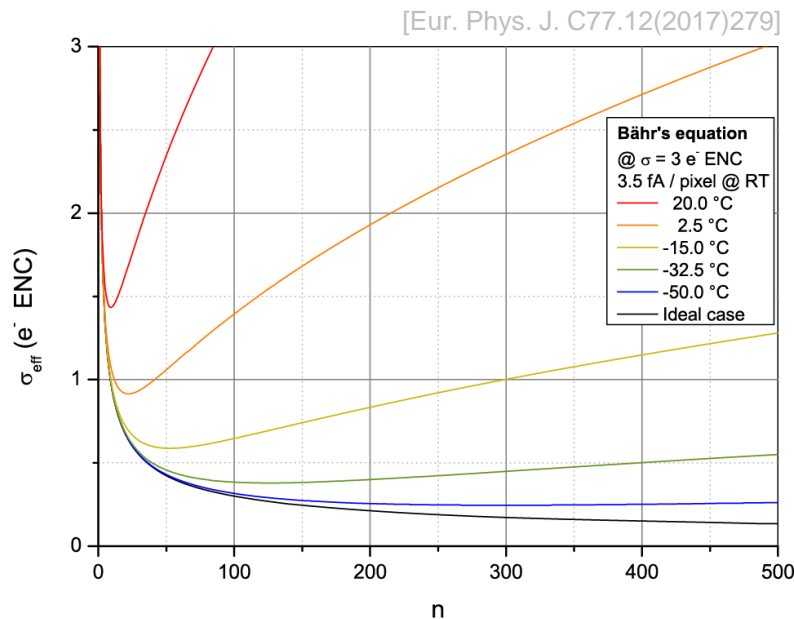


DEPFET-RNDR single pixel performance

Minimal noise limited by leakage current @ 233K (-40°C)

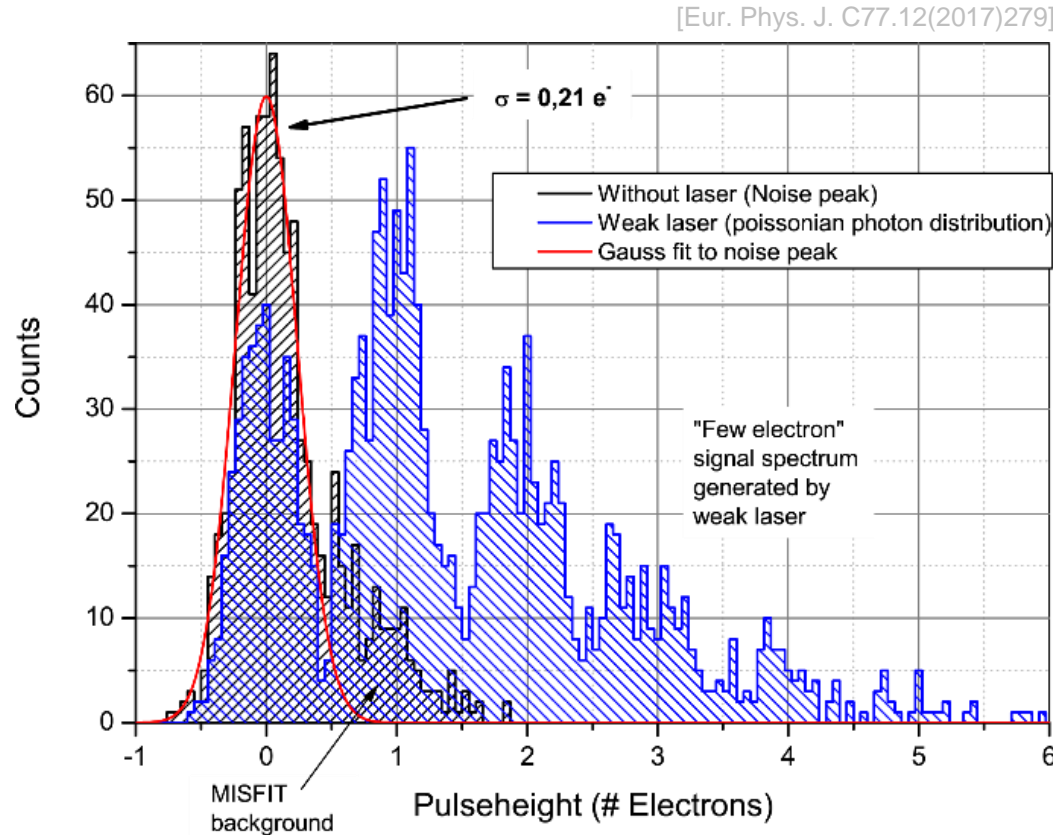


DEPFET-RNDR single pixel performance



Predicted temperature dependence
(only DC from thermal excitation)
- to be verified

DEPFET-RNDR single pixel performance



Single pixel DEPFET-RNDR effective noise:

0.2e⁻ RMS @ 203K(-70°C)

→ Capable to distinguish **single electron** charge

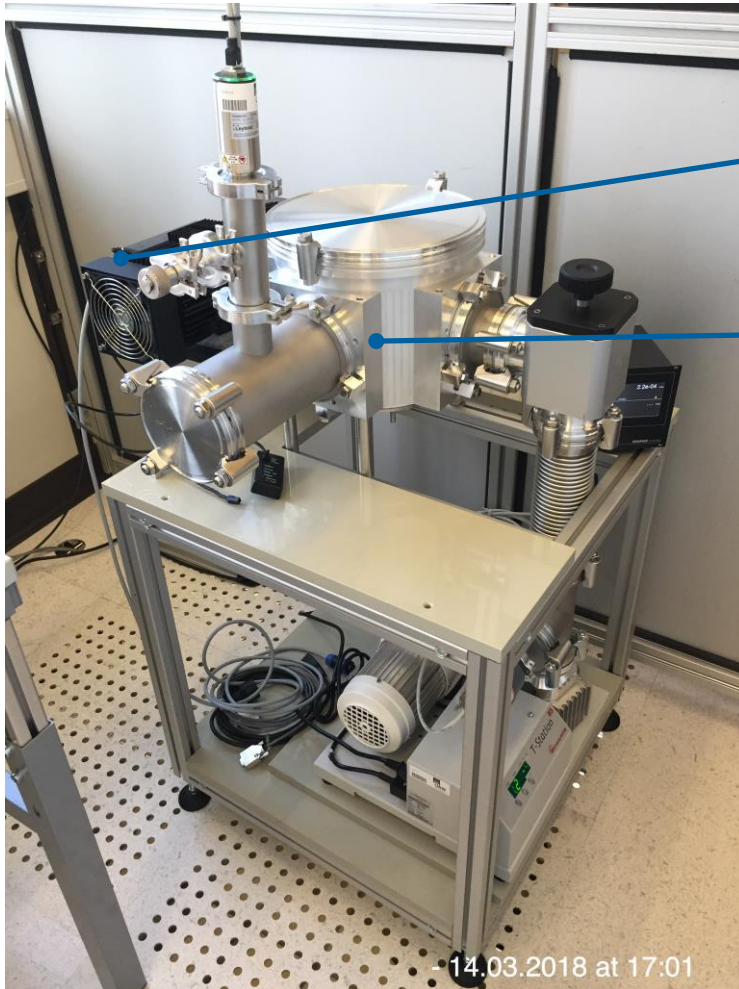
The DANAE project

Direct dArk matter search using DEPFET with repetitive-Non-destructive-readout Application
Experiment

Prototype test setup

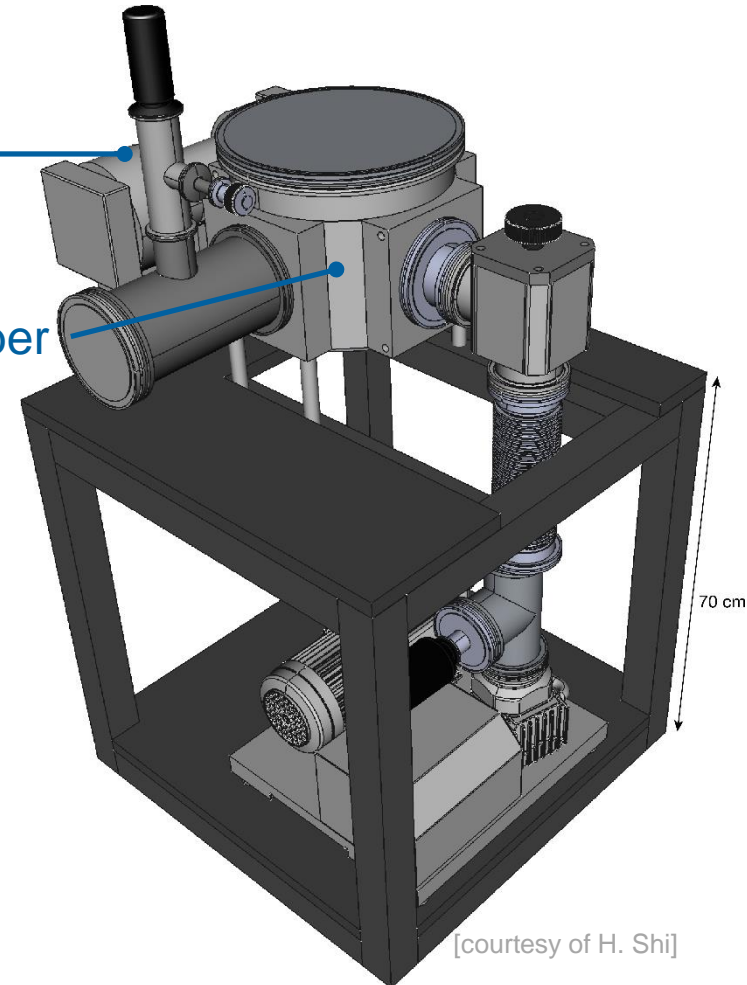
@ HLL

[courtesy of H. Shi]



Stirling-cycle
cryocooler

Vacuum chamber



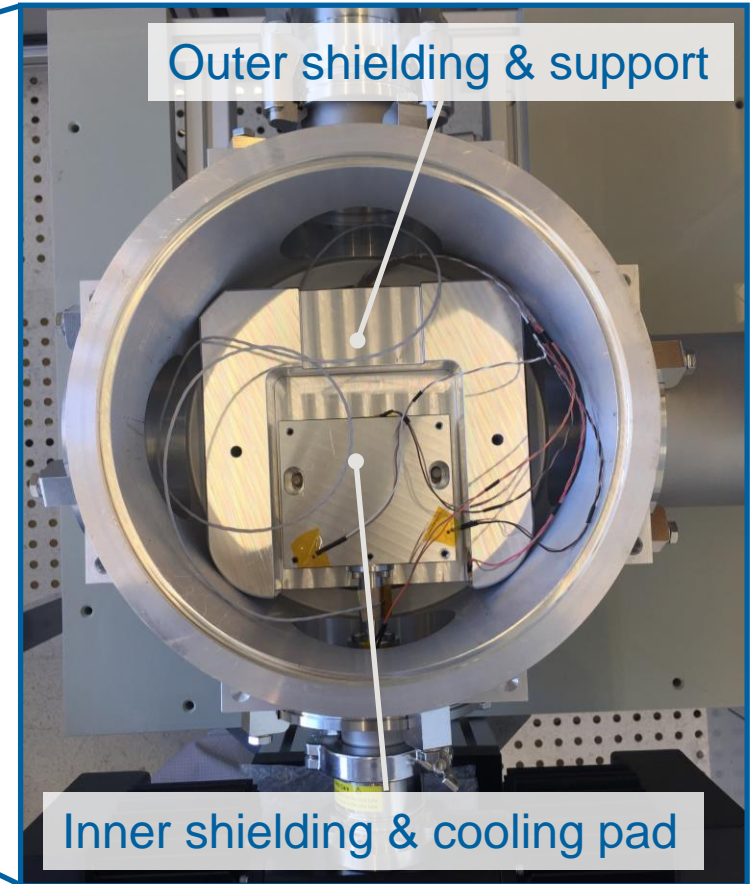
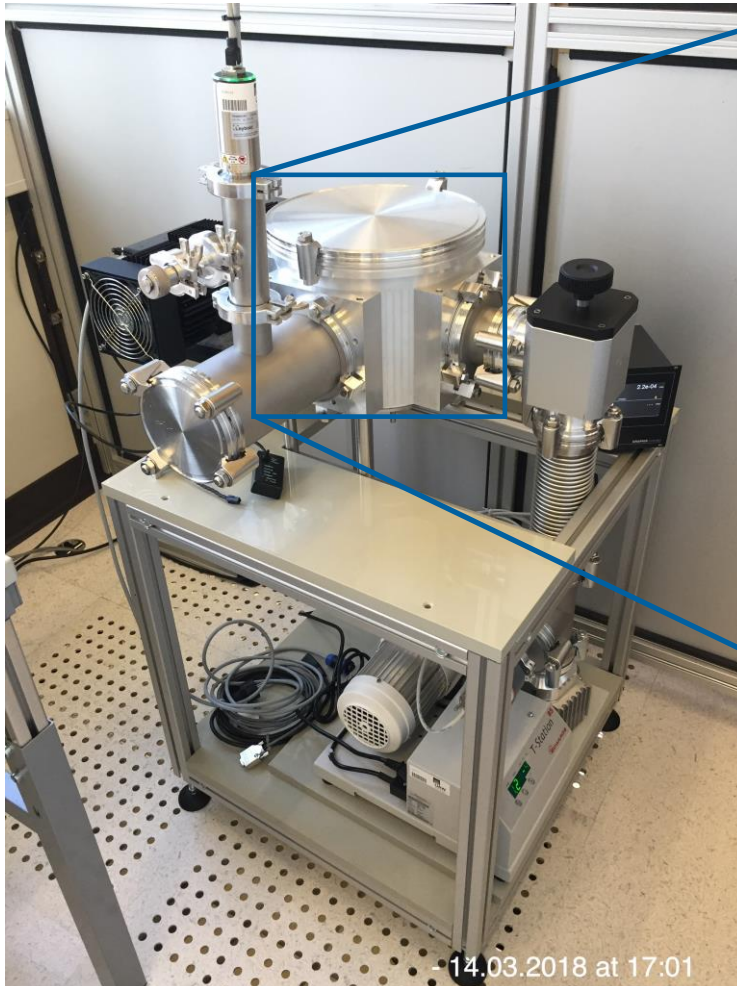
[courtesy of H. Shi]

-14.03.2018 at 17:01

Prototype test setup

@ HLL

[courtesy of H. Shi]



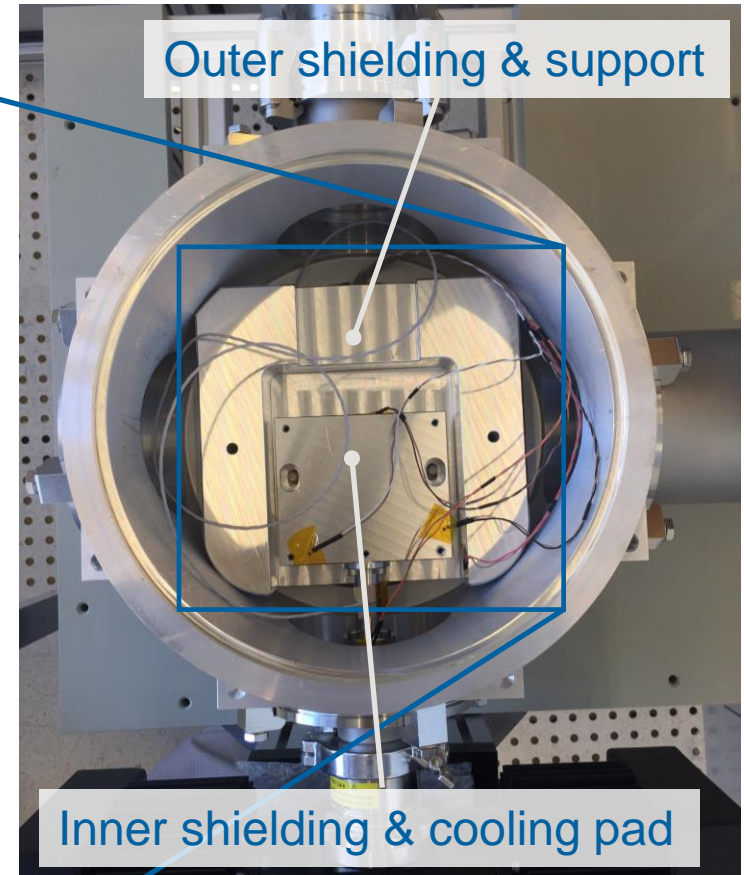
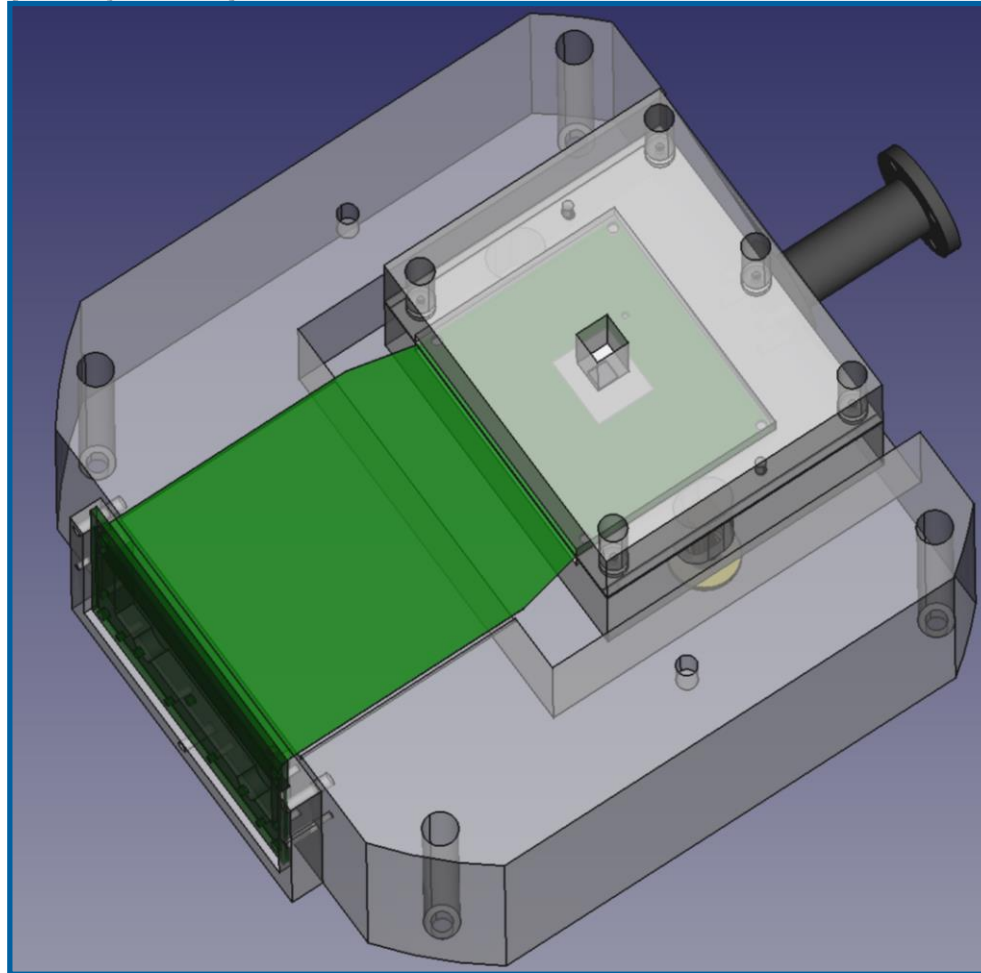
[courtesy of H. Shi]

Vacuum and cooling test in March 2018:
reached 150K @ cooling pad

Prototype test setup

@ HLL

[courtesy of H. Shi]

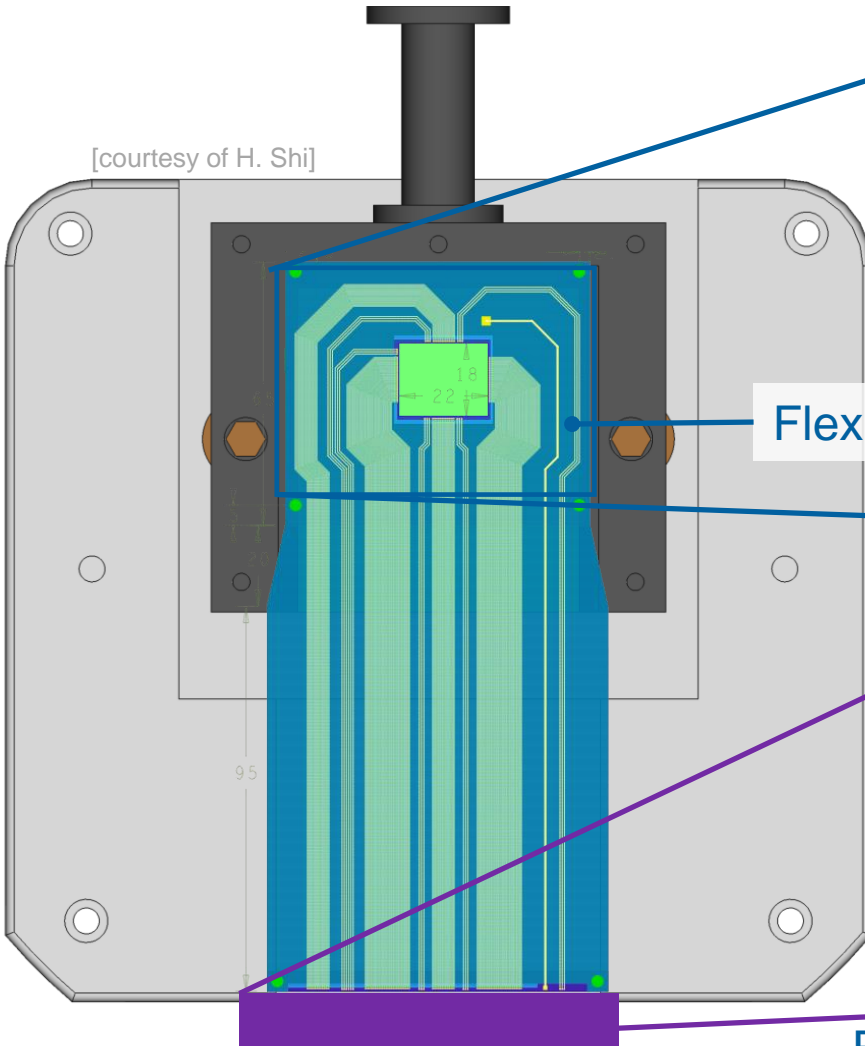


[courtesy of H. Shi]

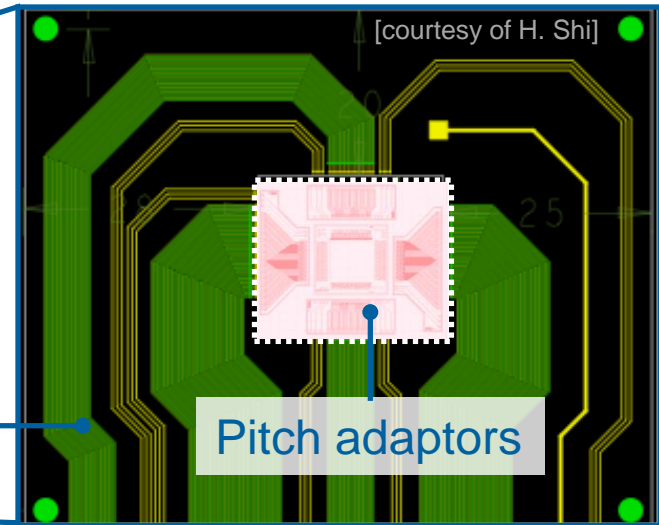
Detector assembly:
to be assembled in mid 2019

Detector control and readout electronics

[courtesy of H. Shi]



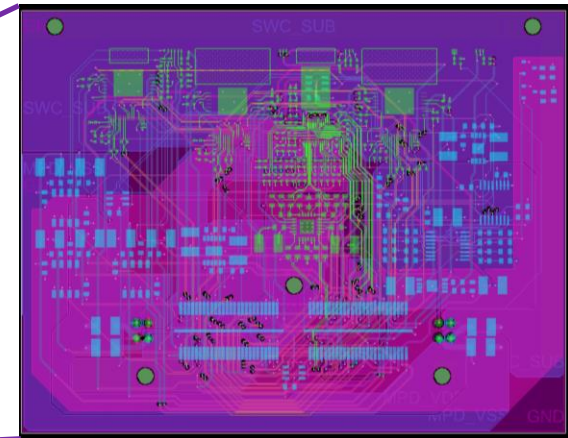
Flexible PCB



[courtesy of H. Shi]

Pitch adaptors

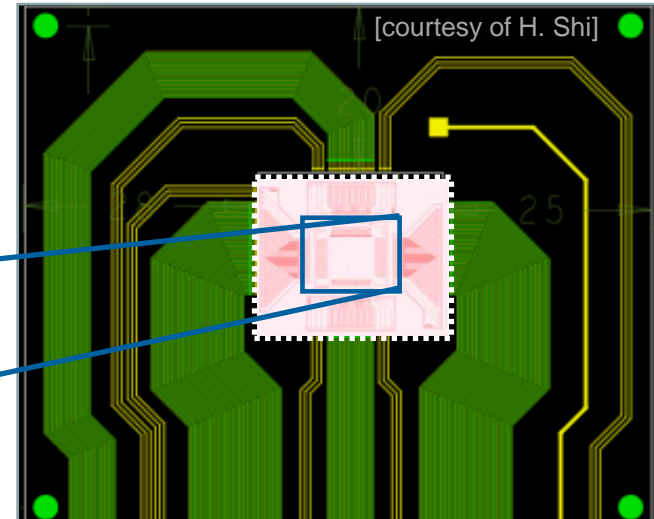
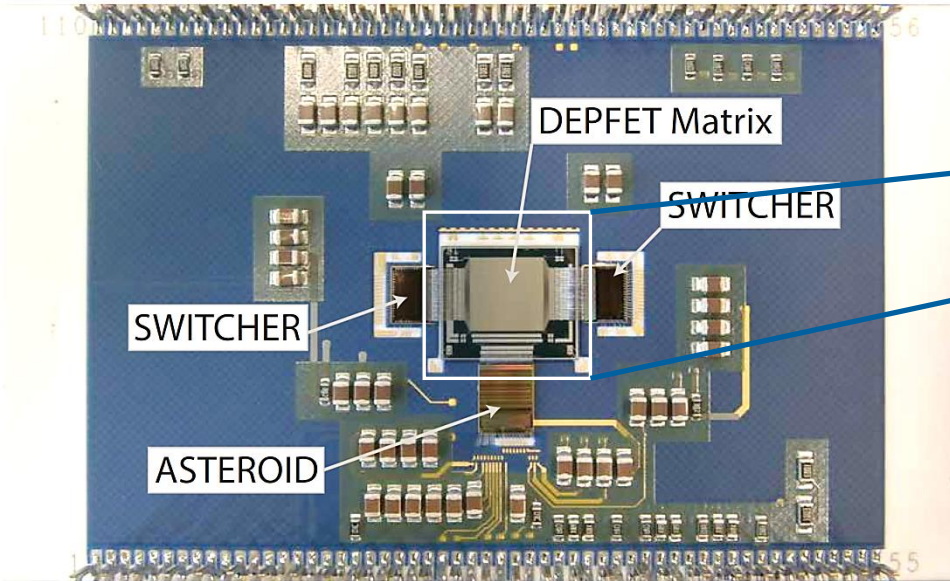
[courtesy of J. Treis]



Readout board: gate-control and readout ASICs

Prototype detector matrix

[courtesy of J. Treis]



Prototype detector matrix:

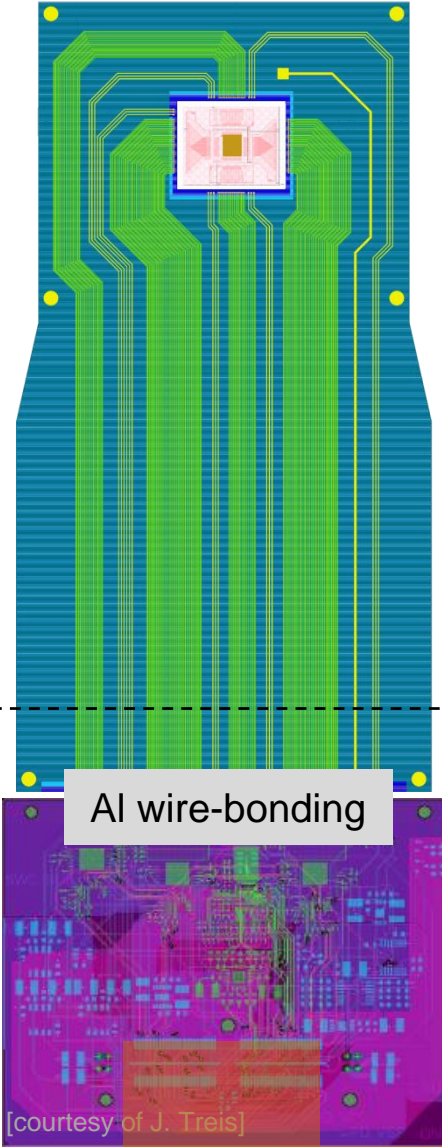
- 64pixel x 64pixel
- Single pixel: $75\mu\text{m} \times 75\mu\text{m} \times 450\mu\text{m}$
- Sensitive volume: **24mg**

[courtesy of H. Shi]

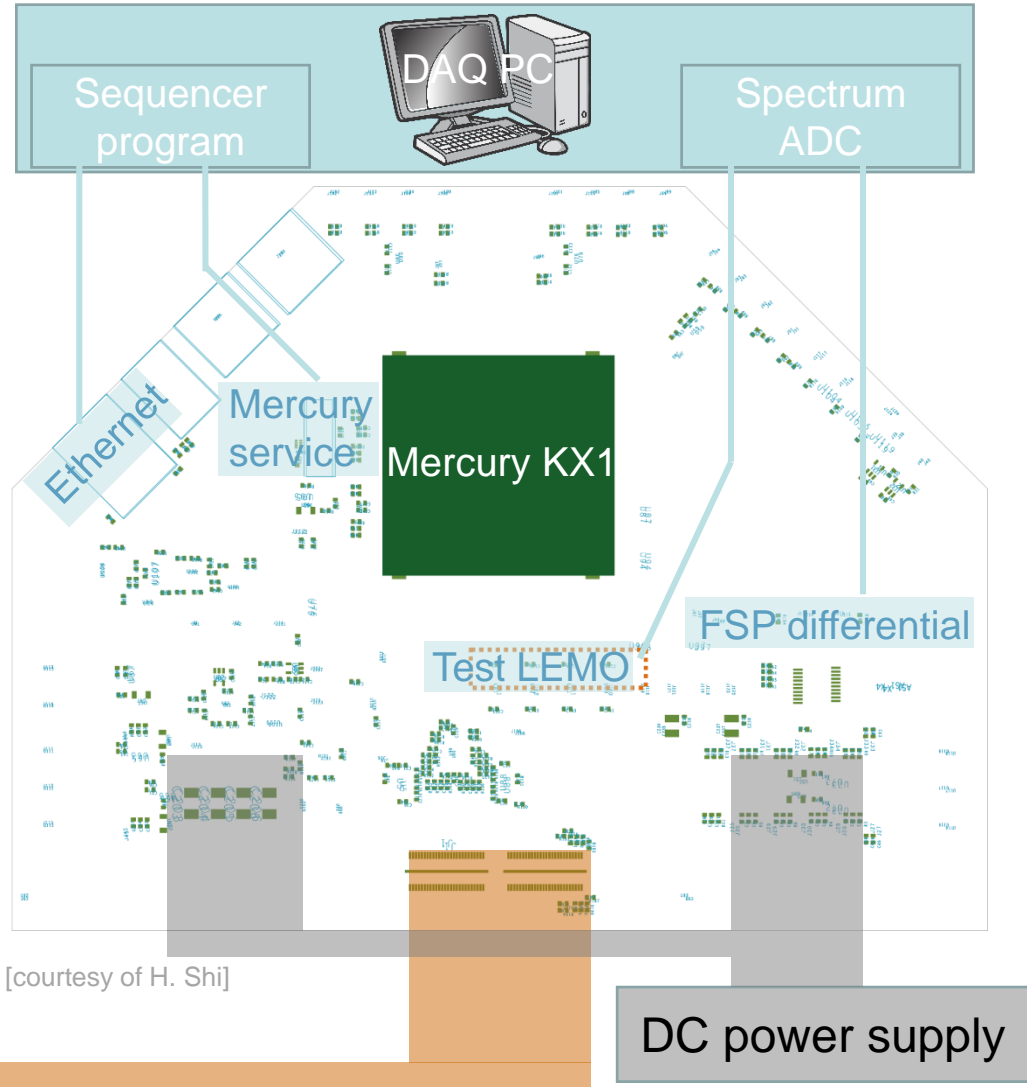
Readout & control

Vacuum ↔ Air

~ -170°C ↔ Room temp.



[courtesy of J. Treis]



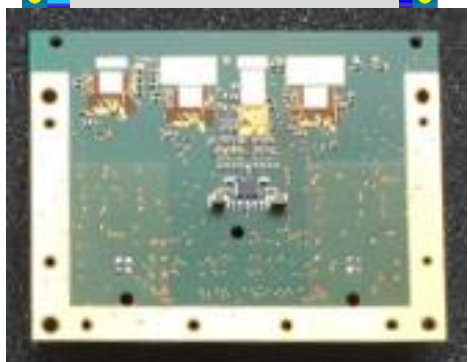
[courtesy of H. Shi]

Components are ready



Vacuum ↔ Air

~ -170°C ↔ Room temp.

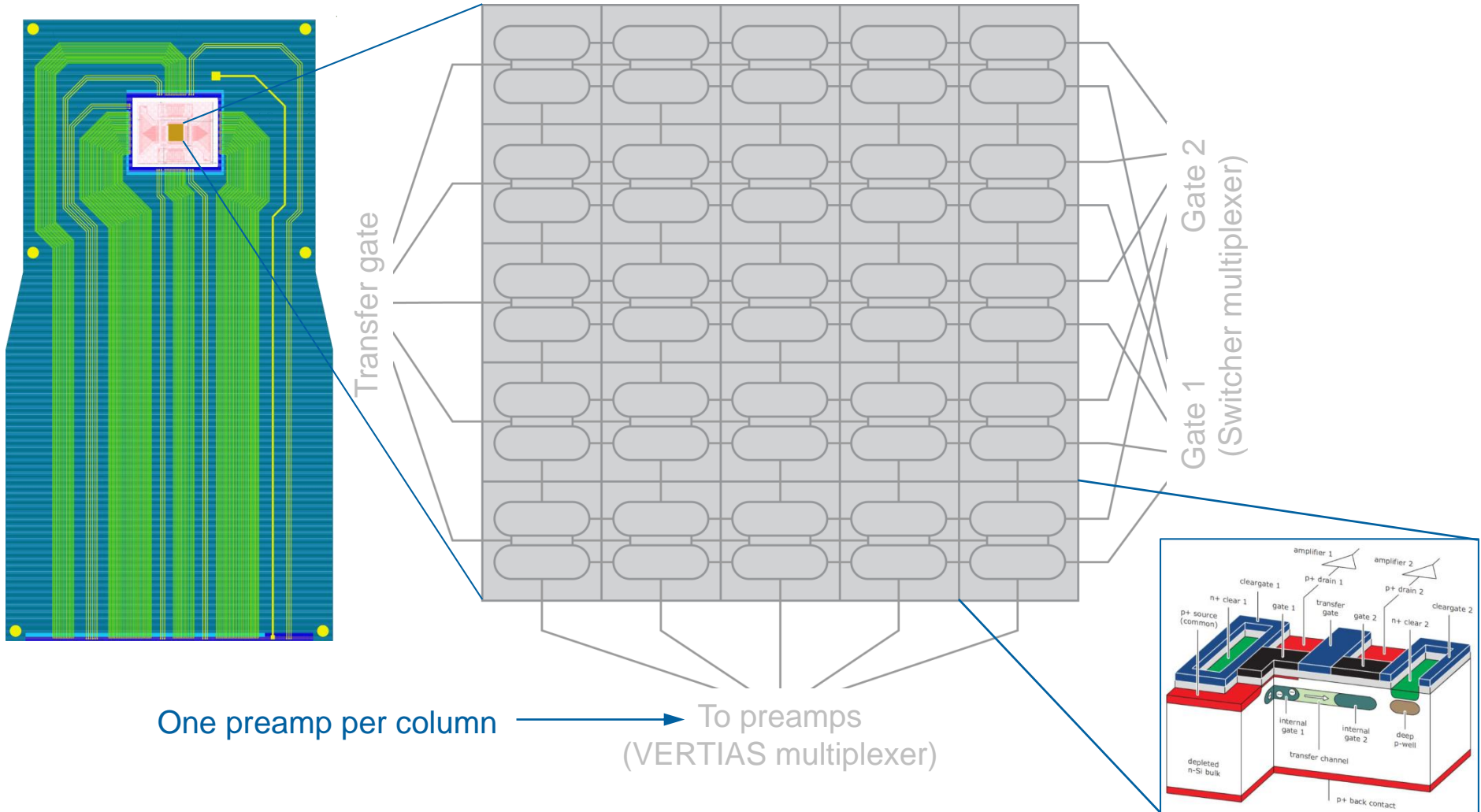


[courtesy of H. Shi]

DC

Read-out sequence

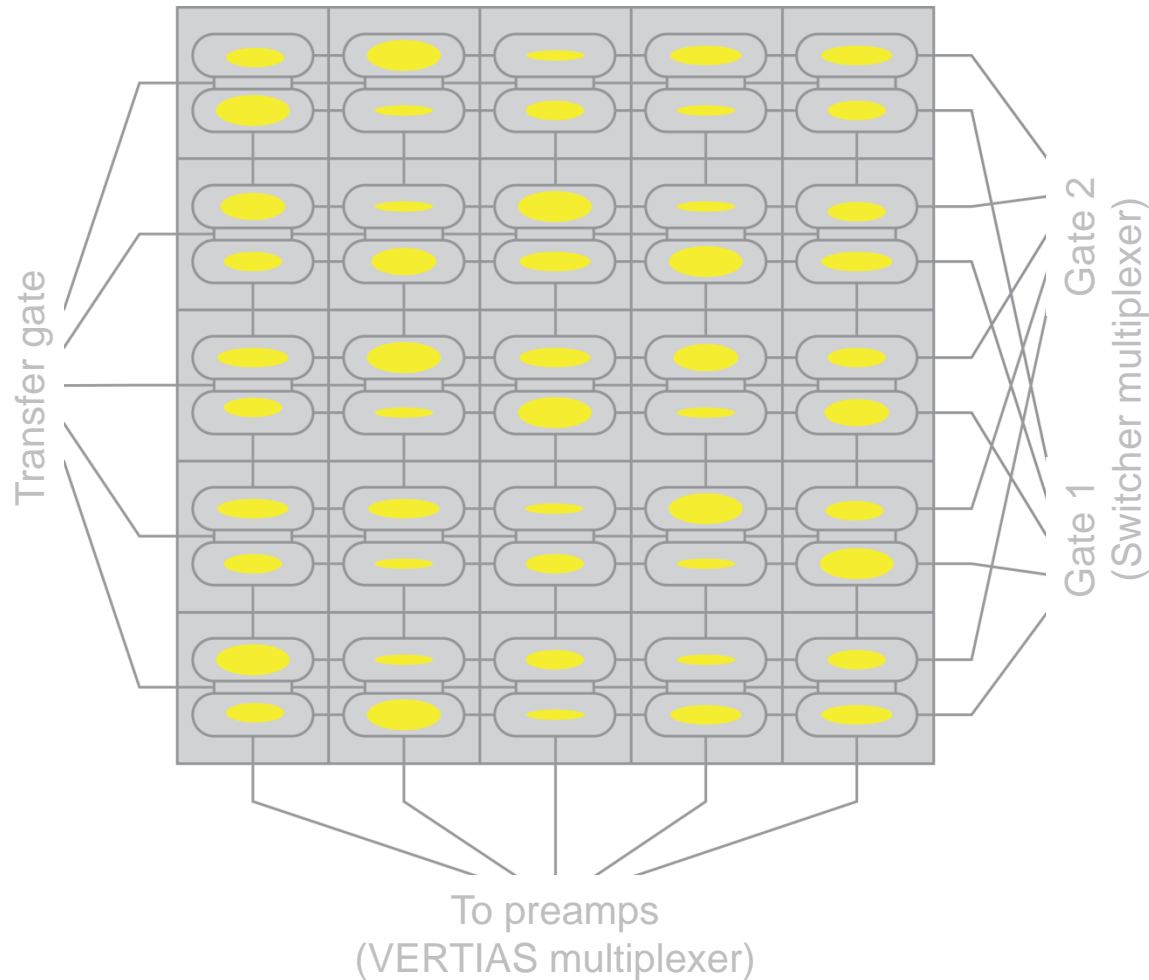
Simplified 5x5 matrix, N=1



Read-out sequence

Simplified 5x5 matrix, N=1

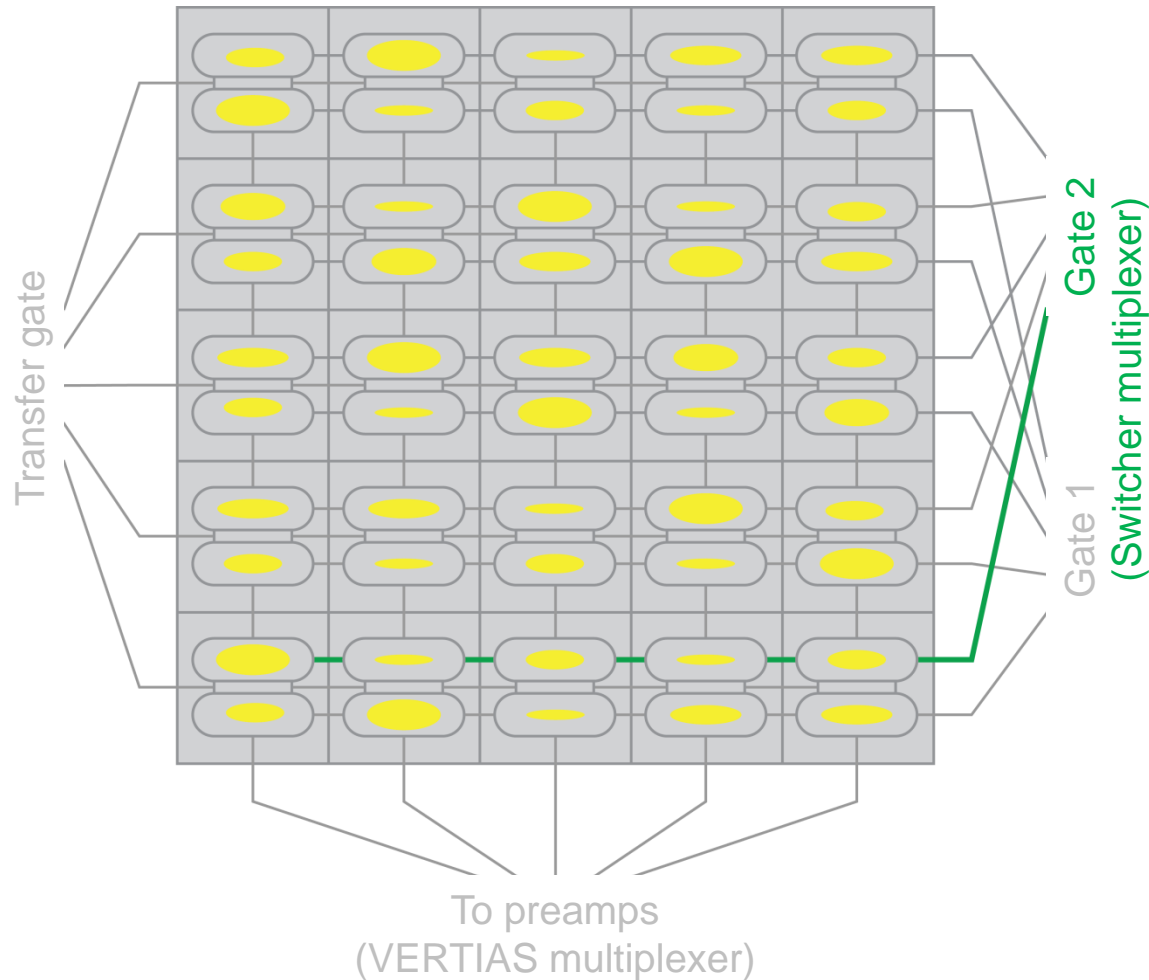
Initial charges



Read-out sequence

Simplified 5x5 matrix, N=1

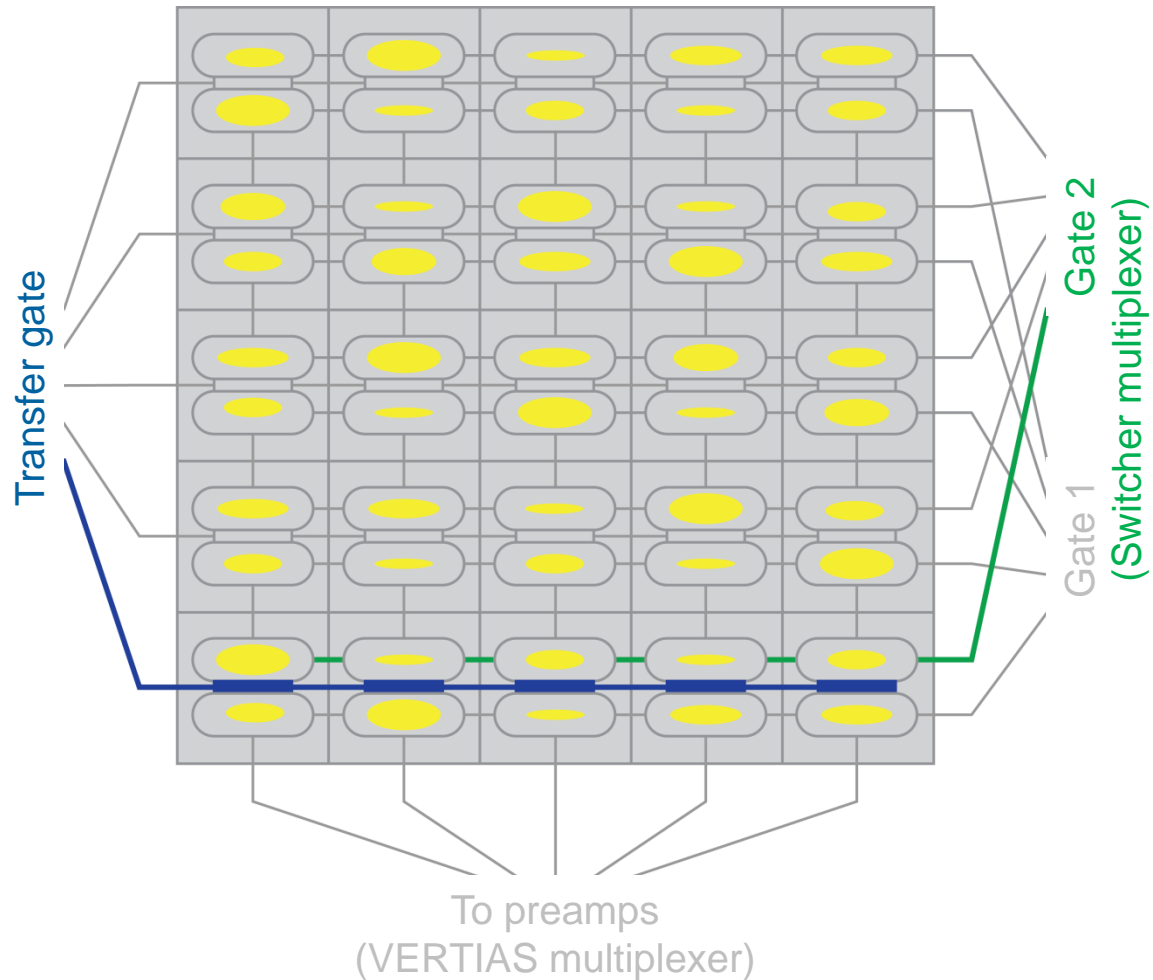
Initial transfer



Read-out sequence

Simplified 5x5 matrix, N=1

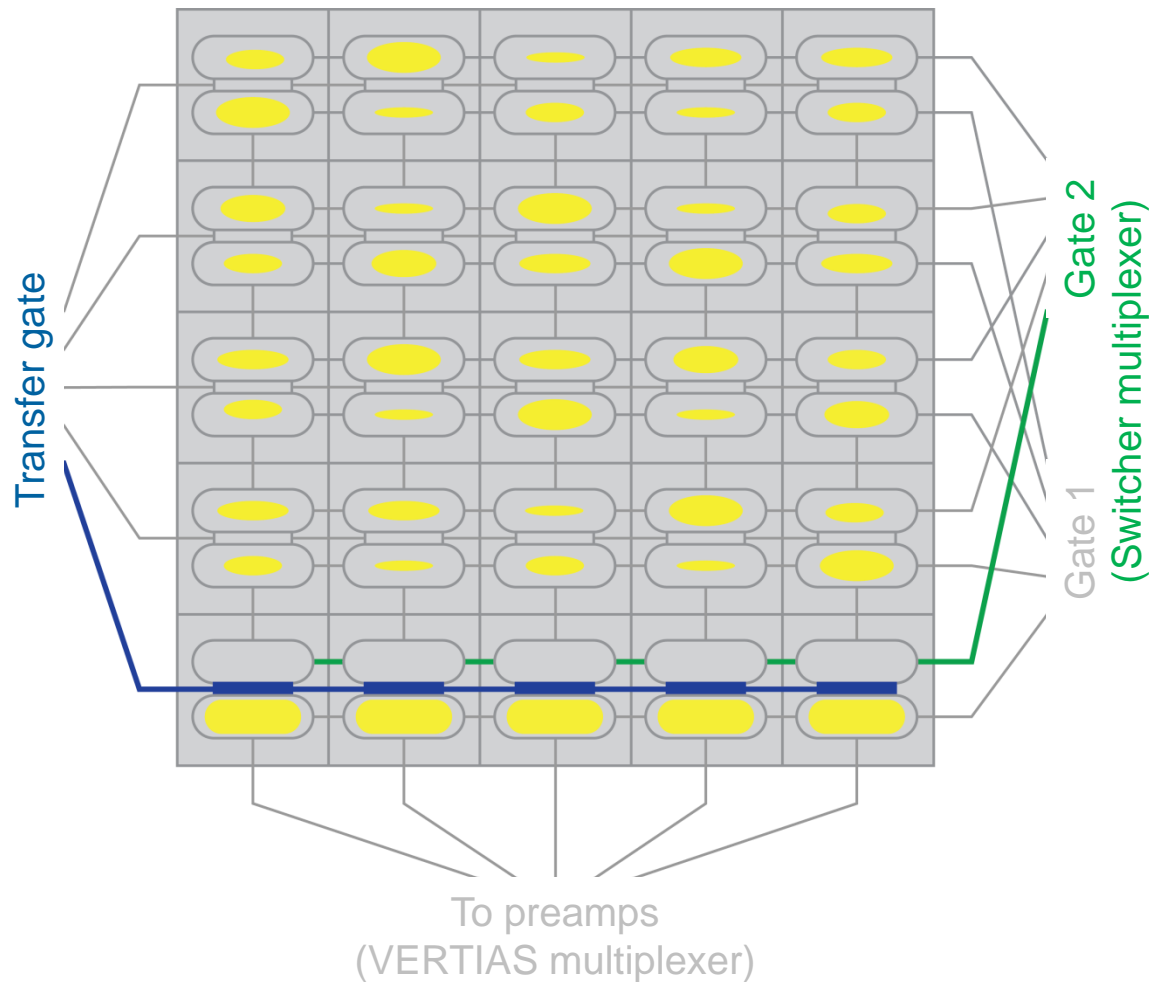
Initial transfer



Read-out sequence

Simplified 5x5 matrix, N=1

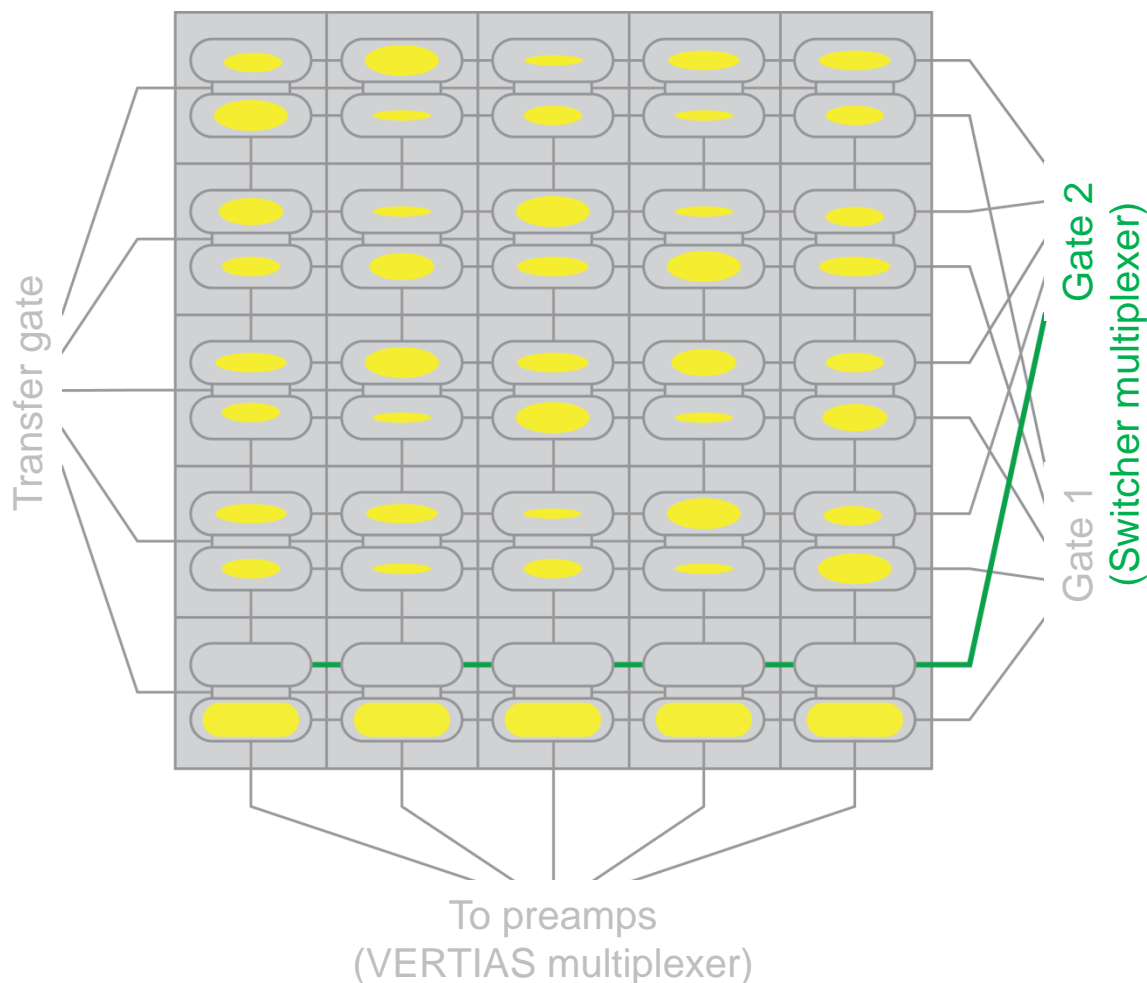
Initial transfer



Read-out sequence

Simplified 5x5 matrix, N=1

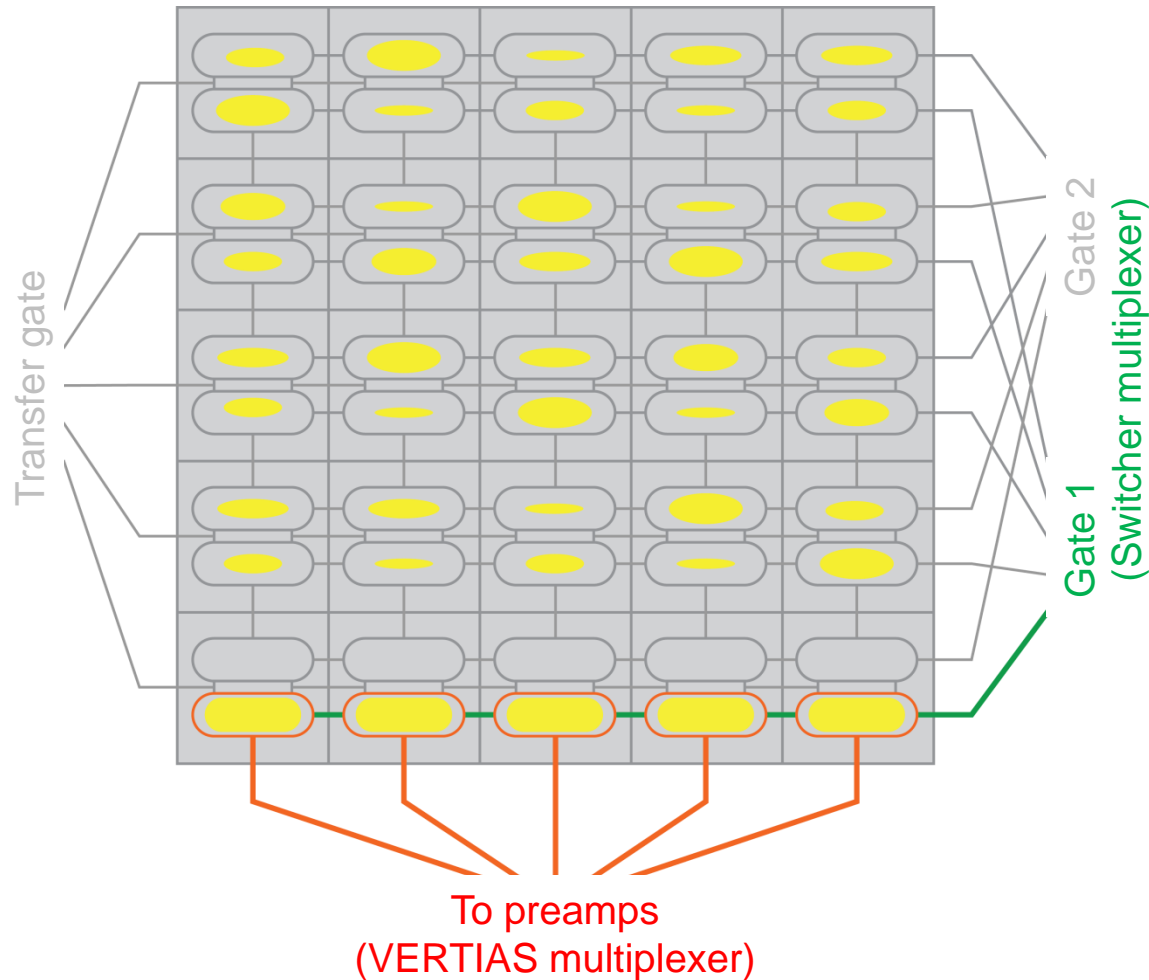
Initial transfer



Read-out sequence

Simplified 5x5 matrix, N=1

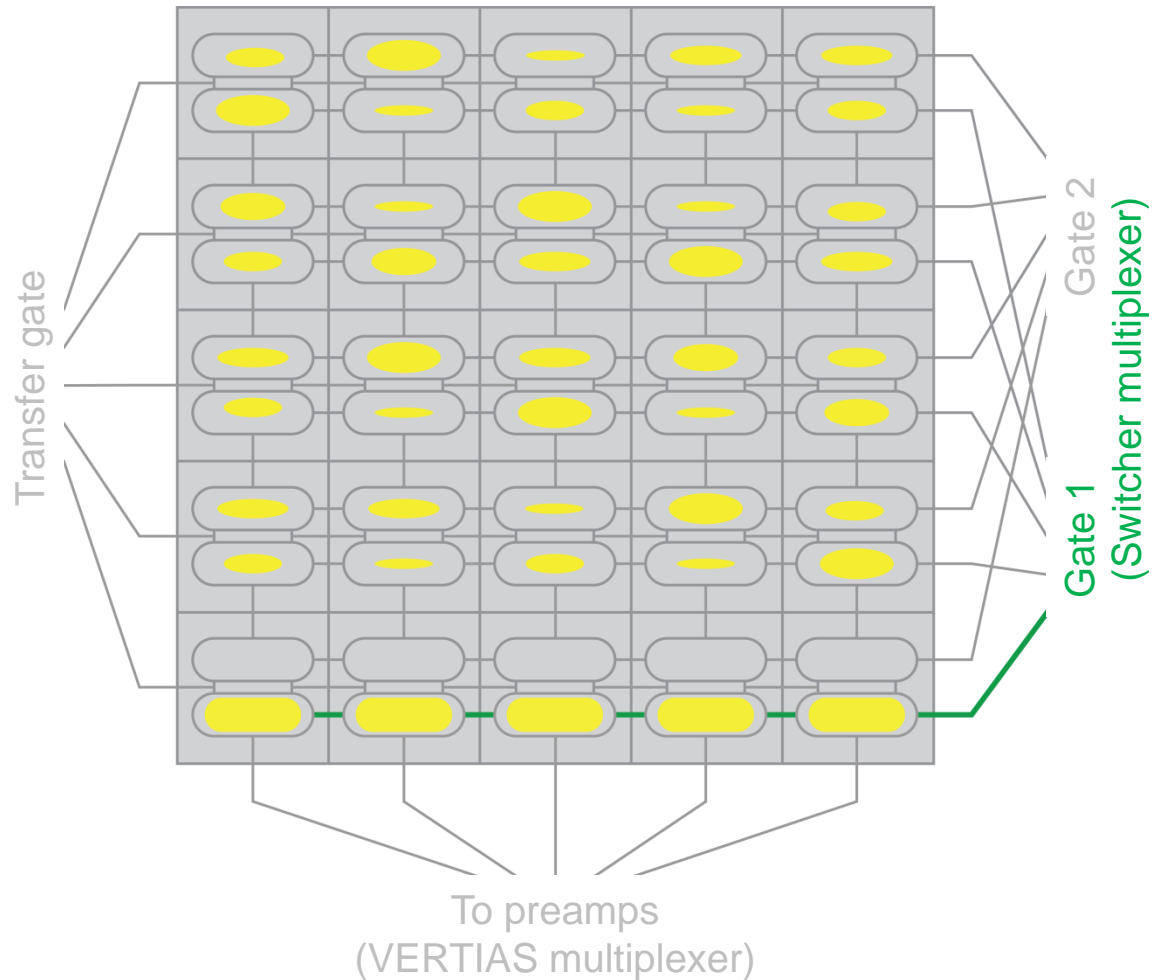
Signal readout 1



Read-out sequence

Simplified 5x5 matrix, N=1

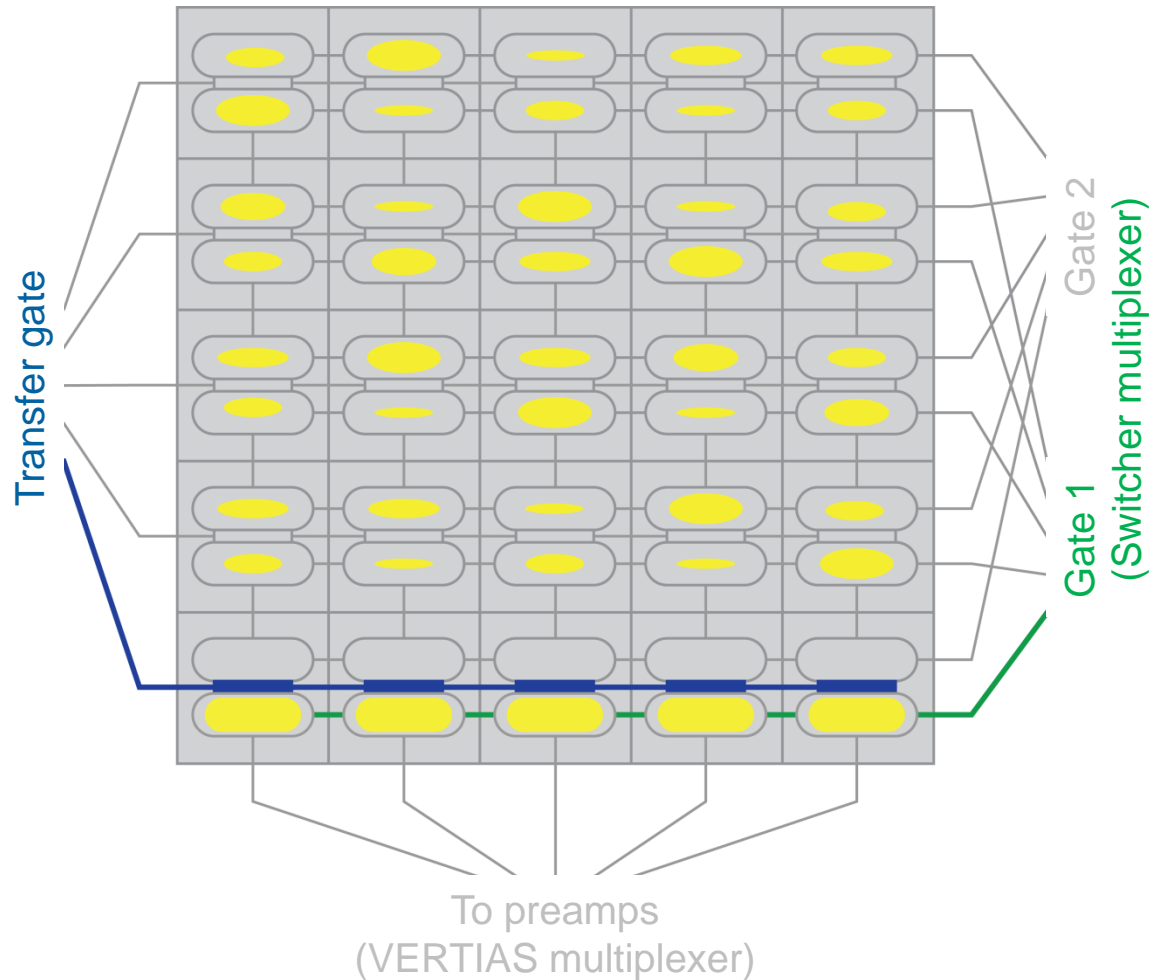
Signal transfer



Read-out sequence

Simplified 5x5 matrix, N=1

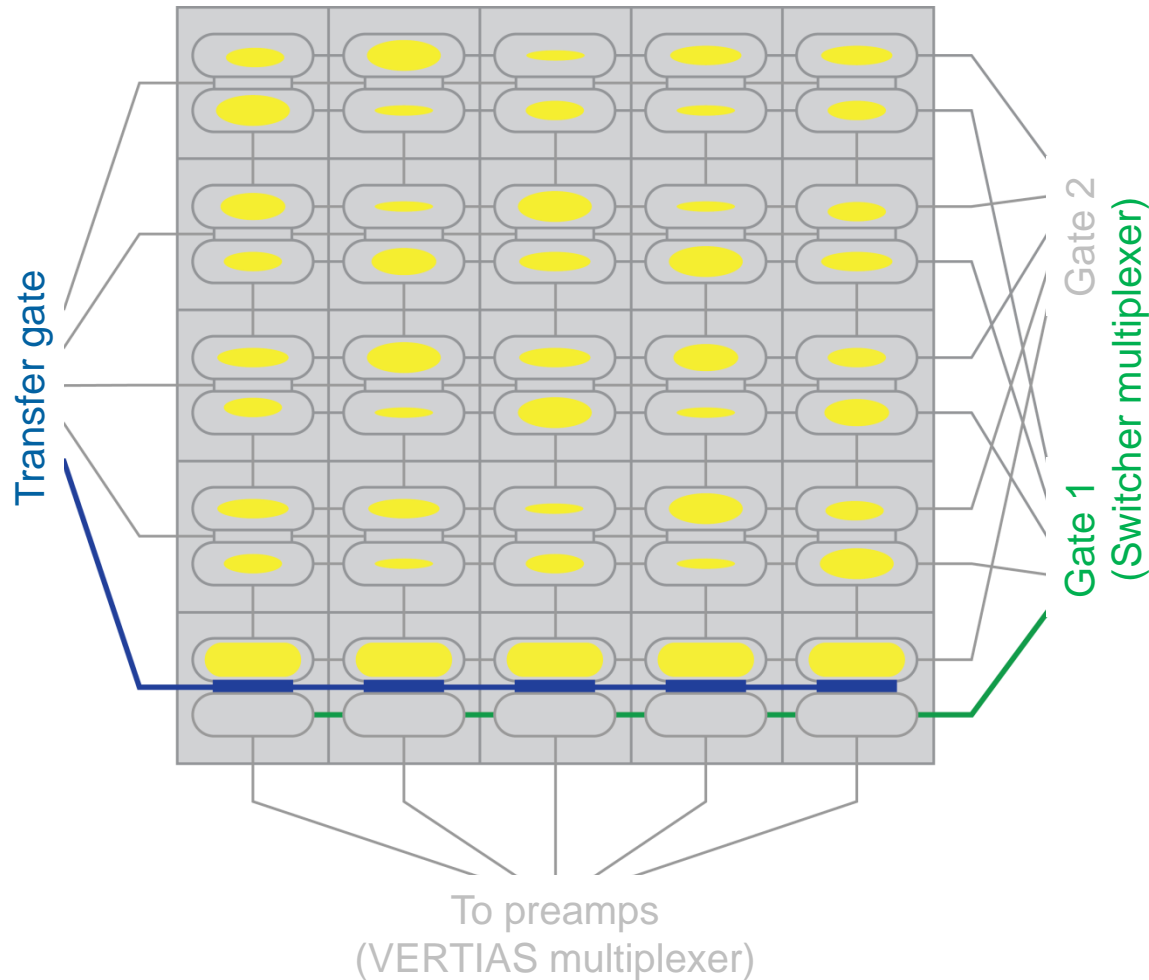
Signal transfer



Read-out sequence

Simplified 5x5 matrix, N=1

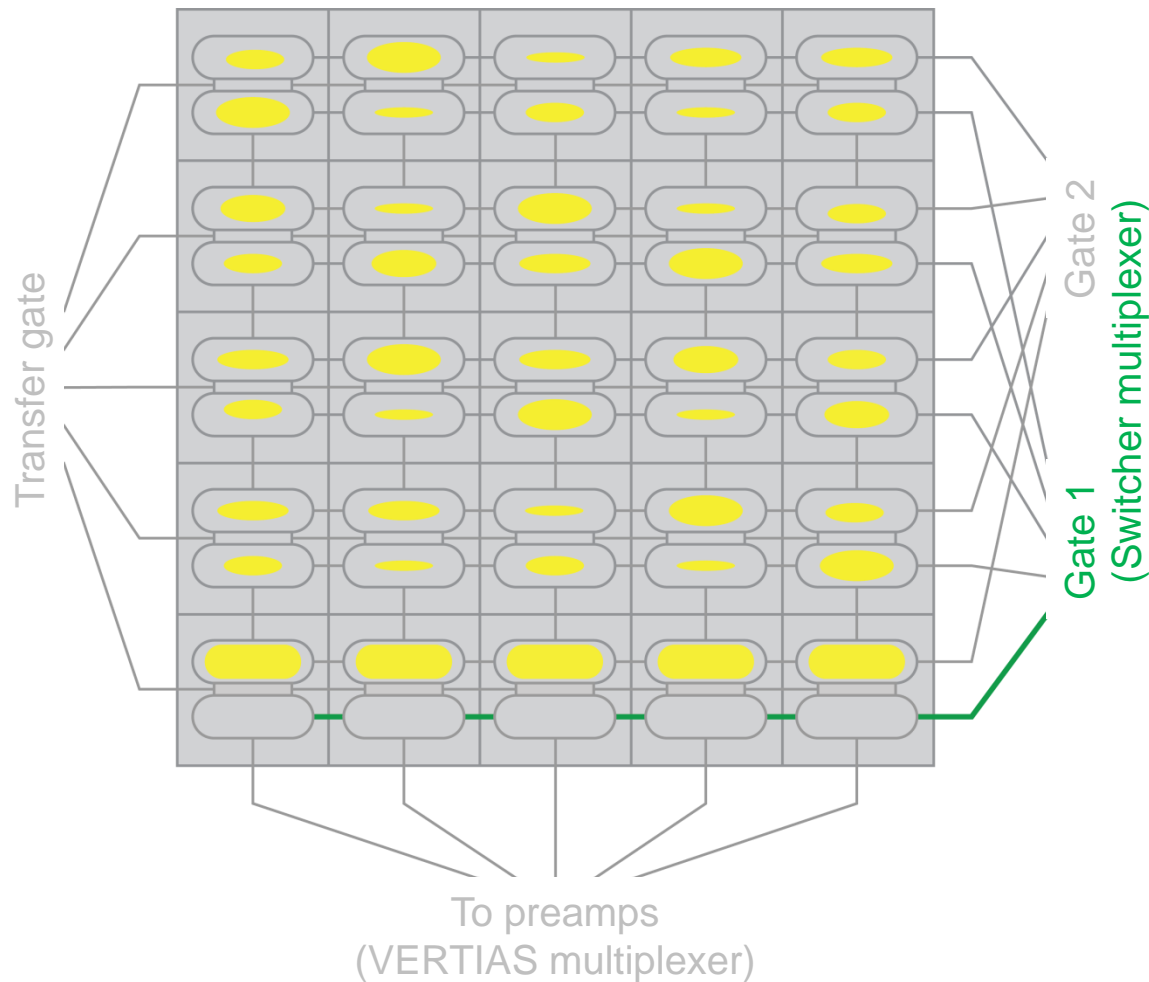
Signal transfer



Read-out sequence

Simplified 5x5 matrix, N=1

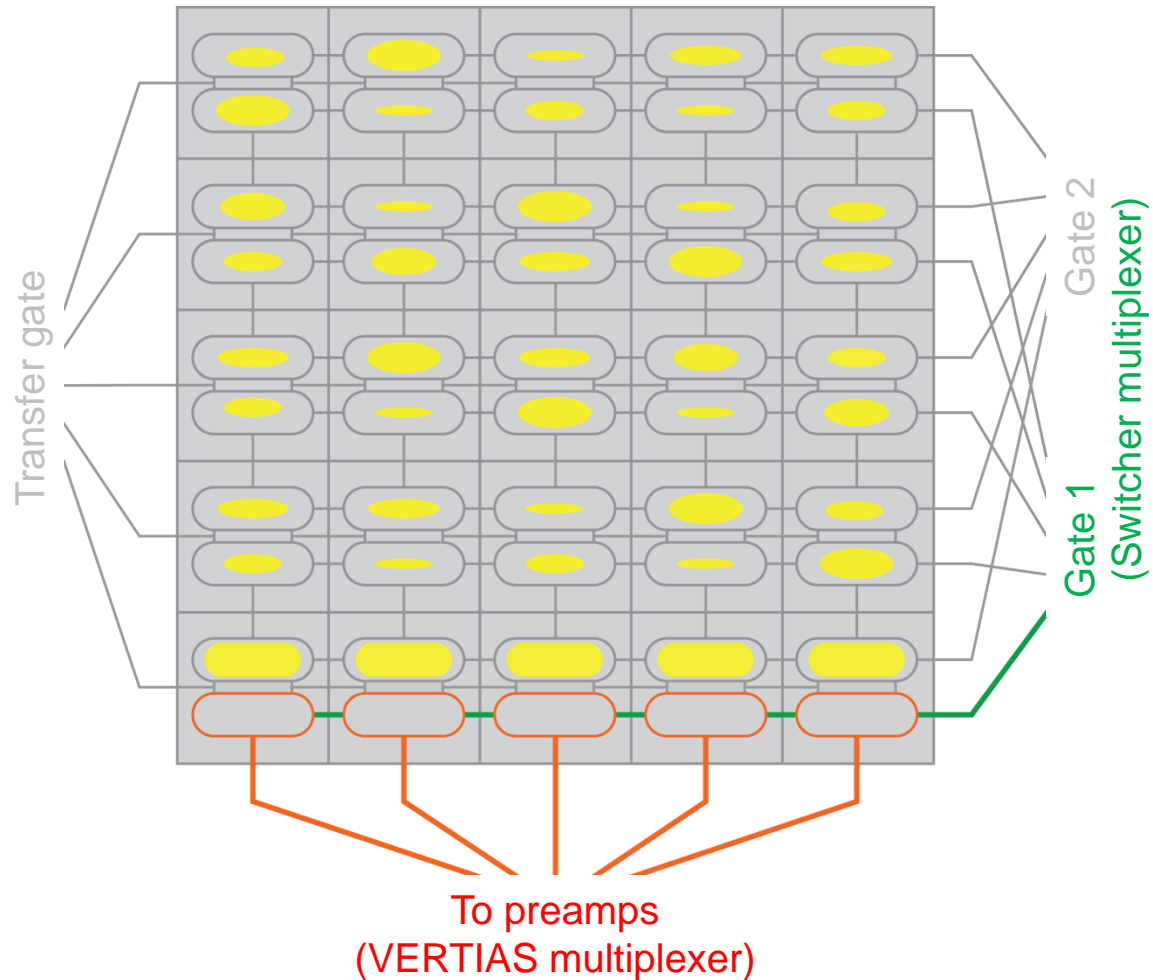
Signal transfer



Read-out sequence

Simplified 5x5 matrix, N=1

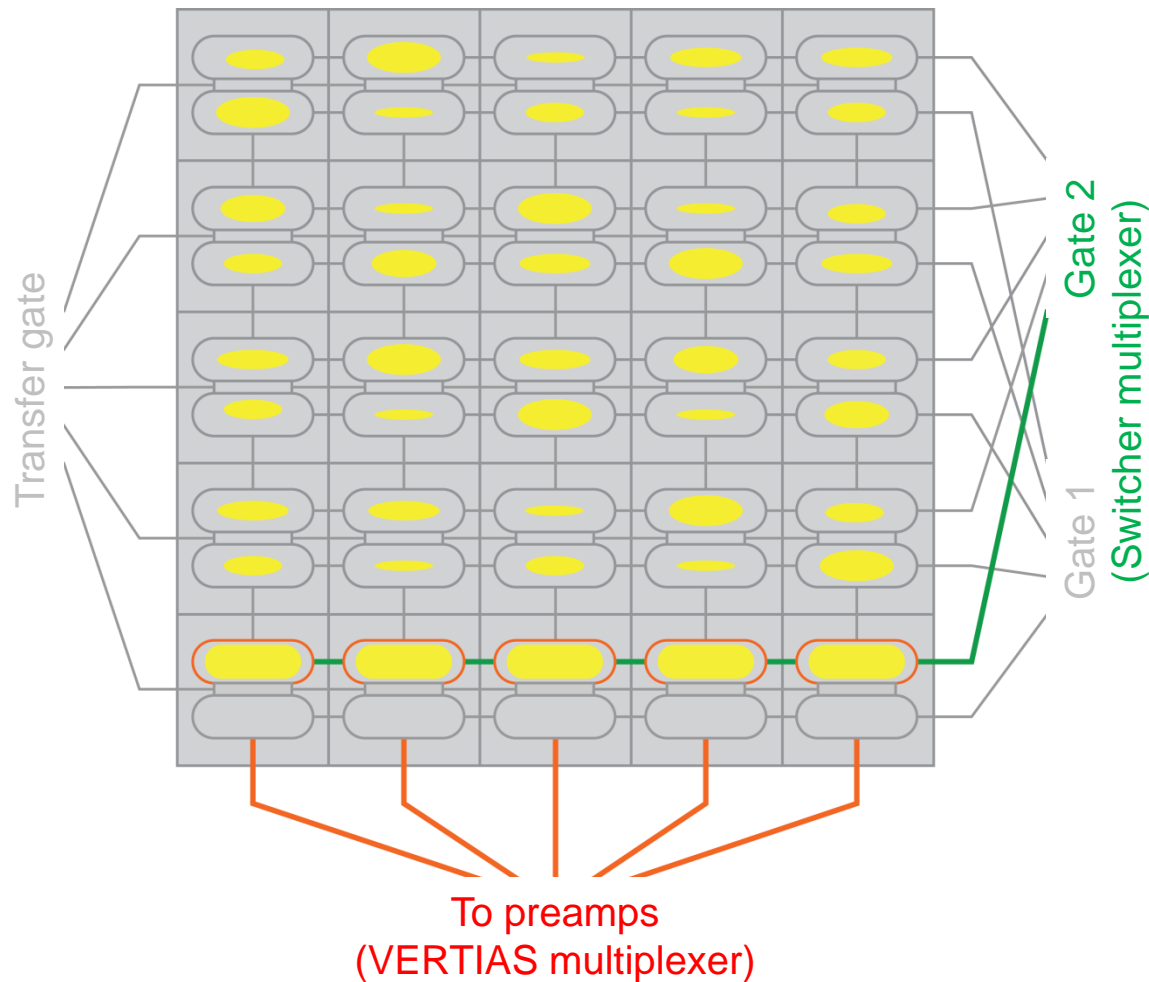
Baseline readout 1



Read-out sequence

Simplified 5x5 matrix, N=1

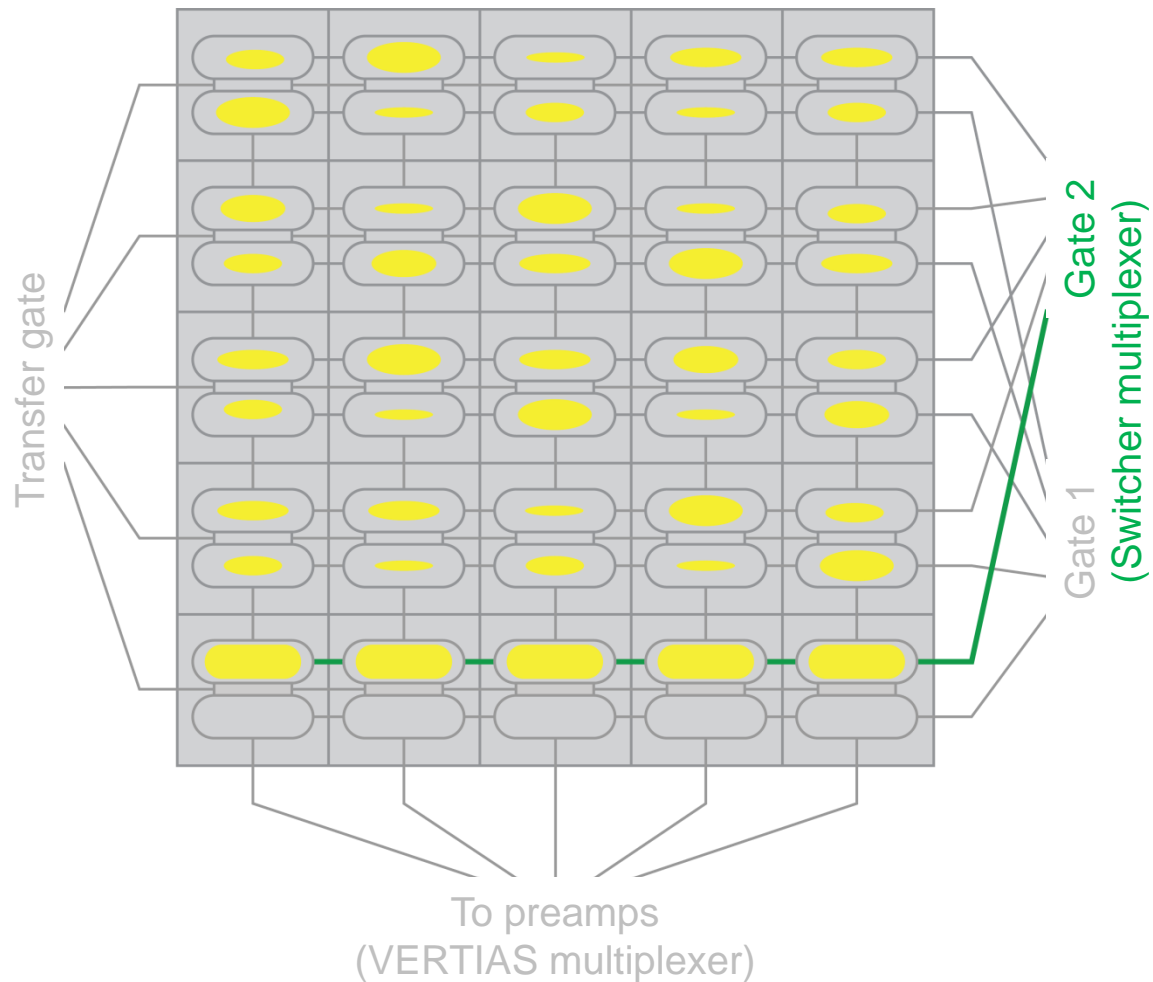
Signal readout 2



Read-out sequence

Simplified 5x5 matrix, N=1

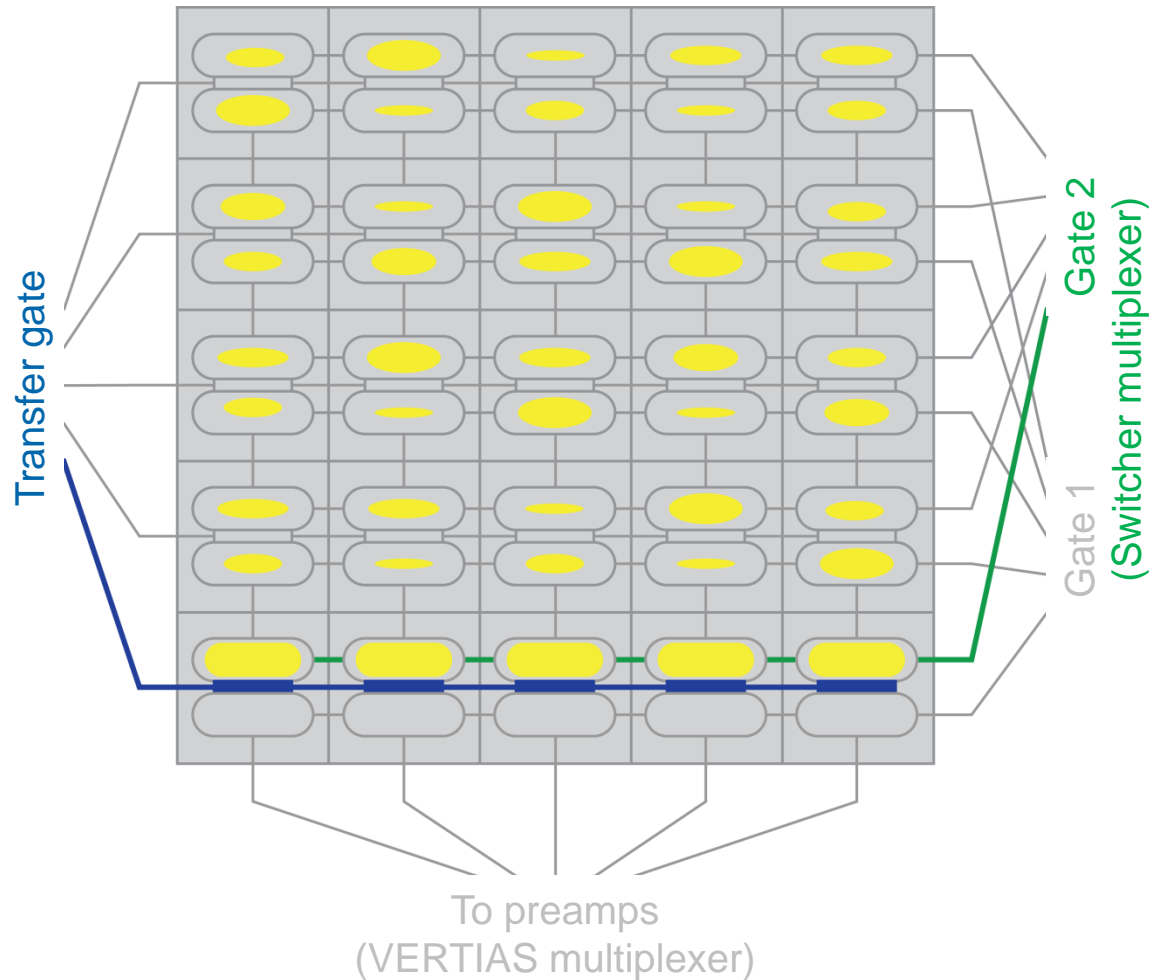
Signal transfer



Read-out sequence

Simplified 5x5 matrix, N=1

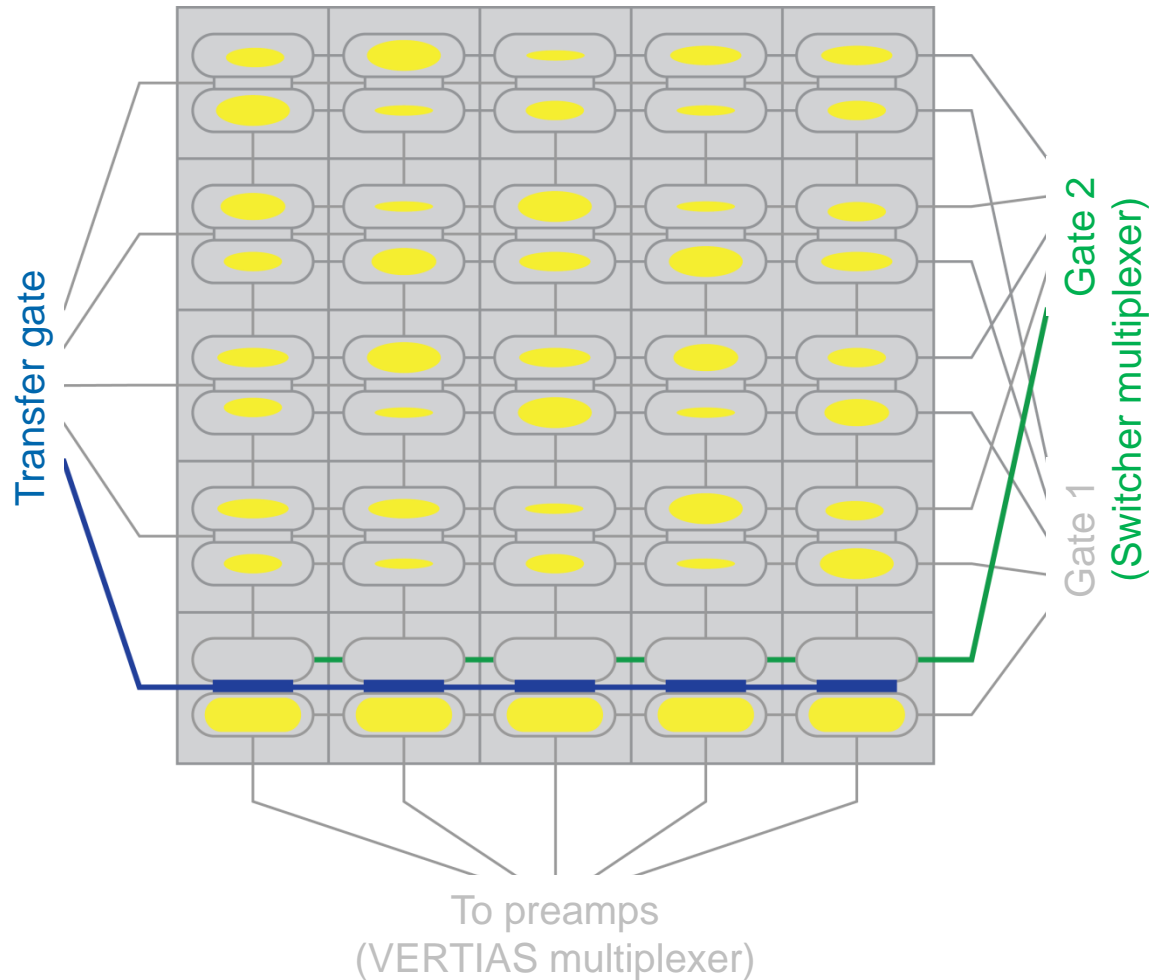
Signal transfer



Read-out sequence

Simplified 5x5 matrix, N=1

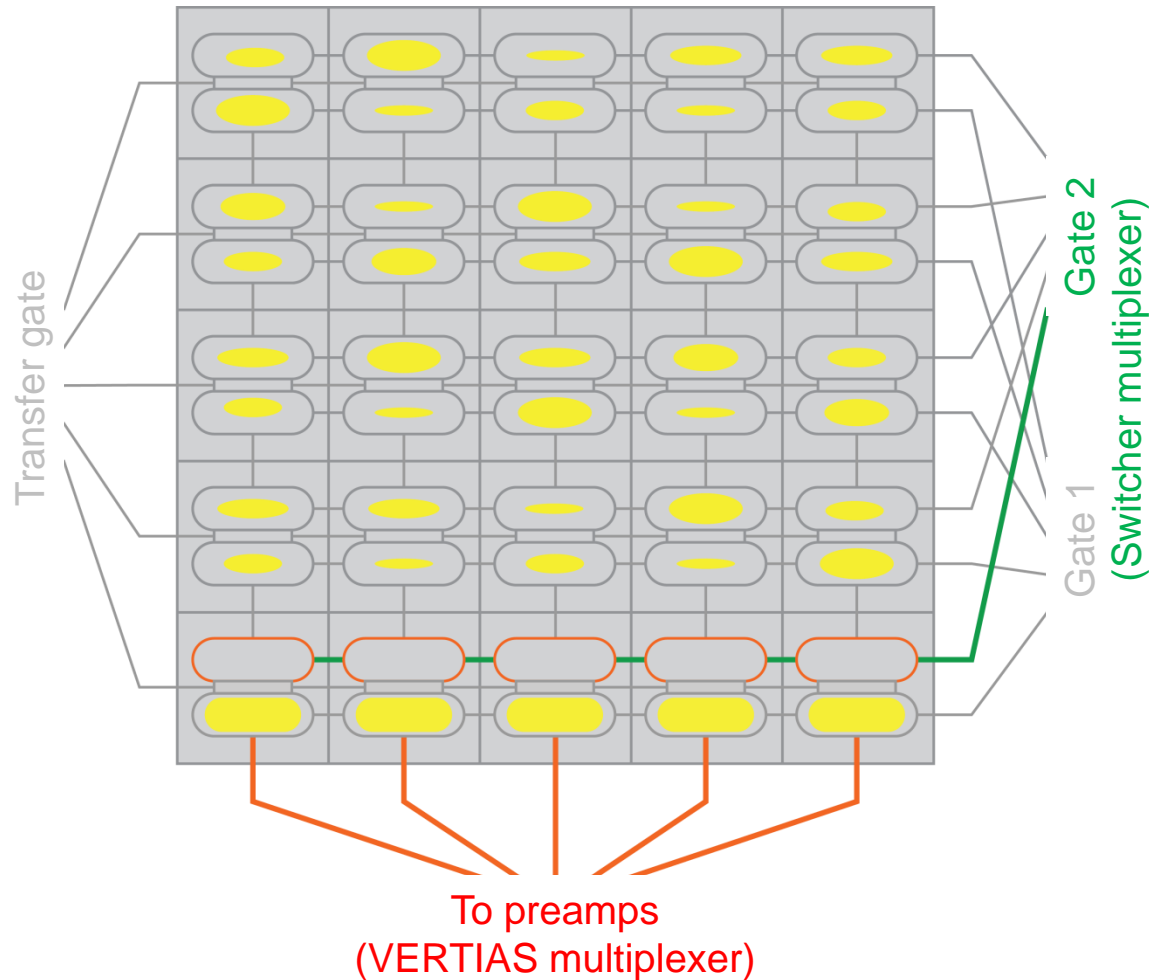
Signal transfer



Read-out sequence

Simplified 5x5 matrix, N=1

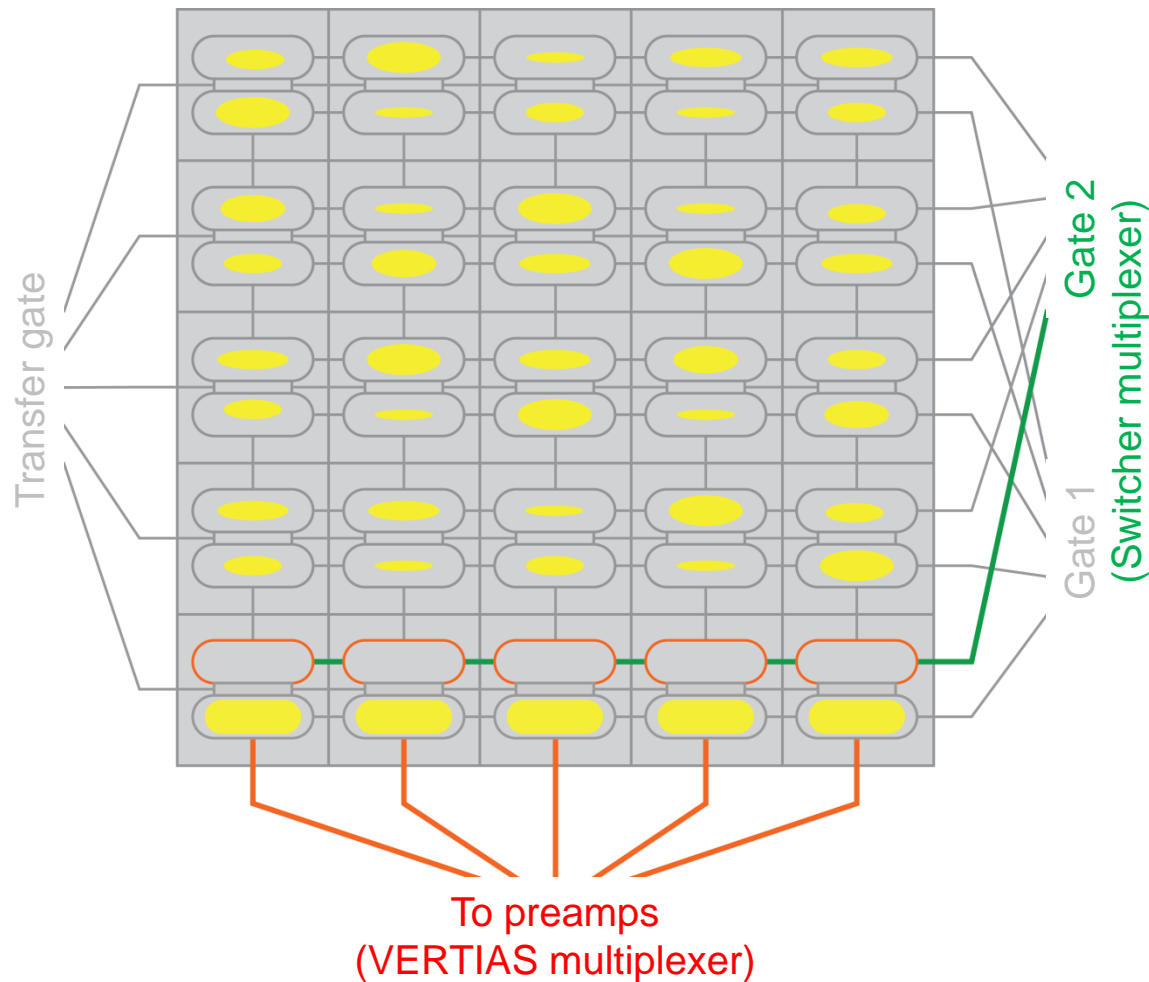
Baseline readout 2



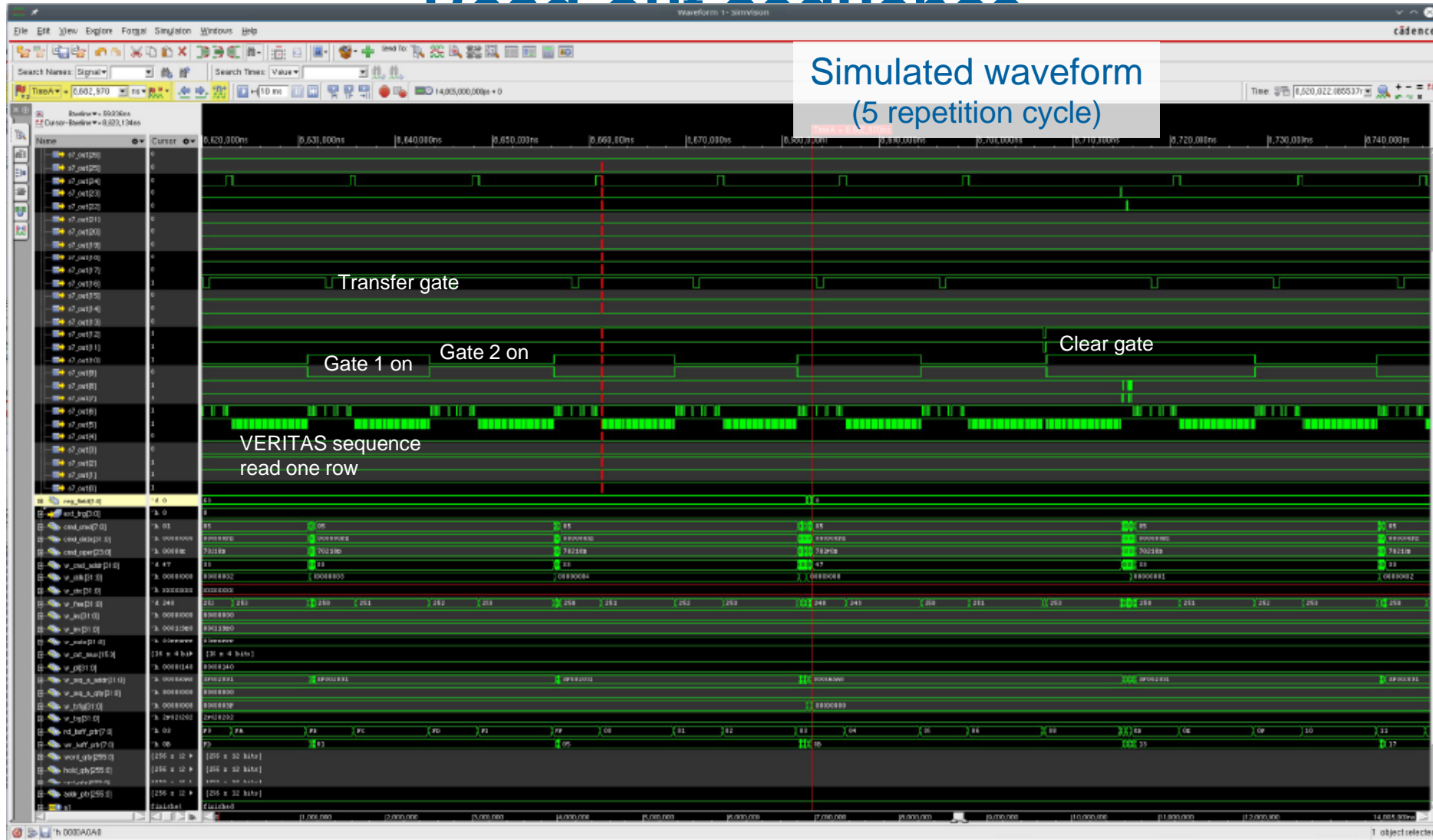
Read-out sequence

Simplified 5x5 matrix, N=1

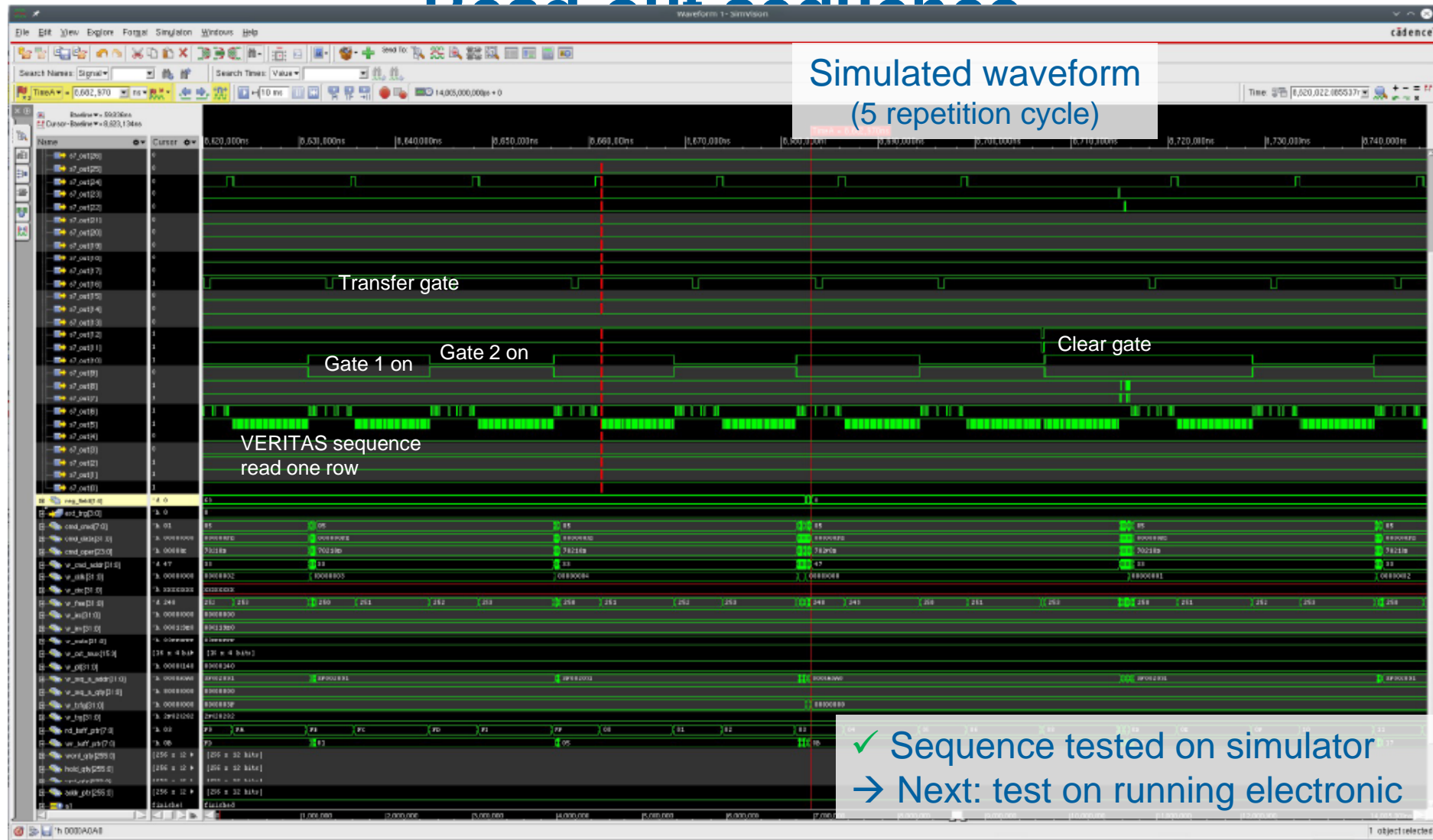
Repeat N-times
Go on to next row



Readout sequence

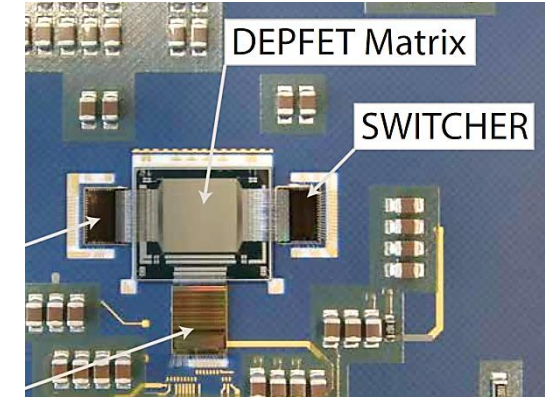


Read out sequence



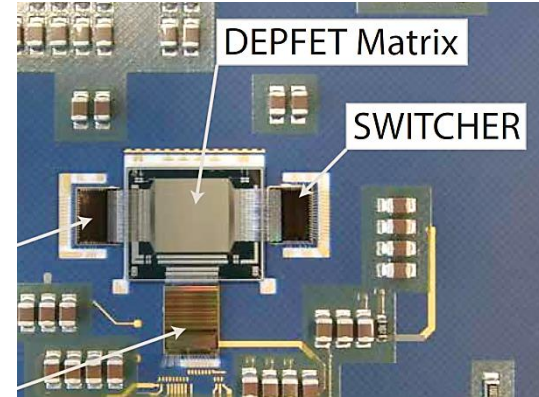
Physics perspective

- Expect preliminary results from the prototype setup (24 mg sensitive volume) in late 2019

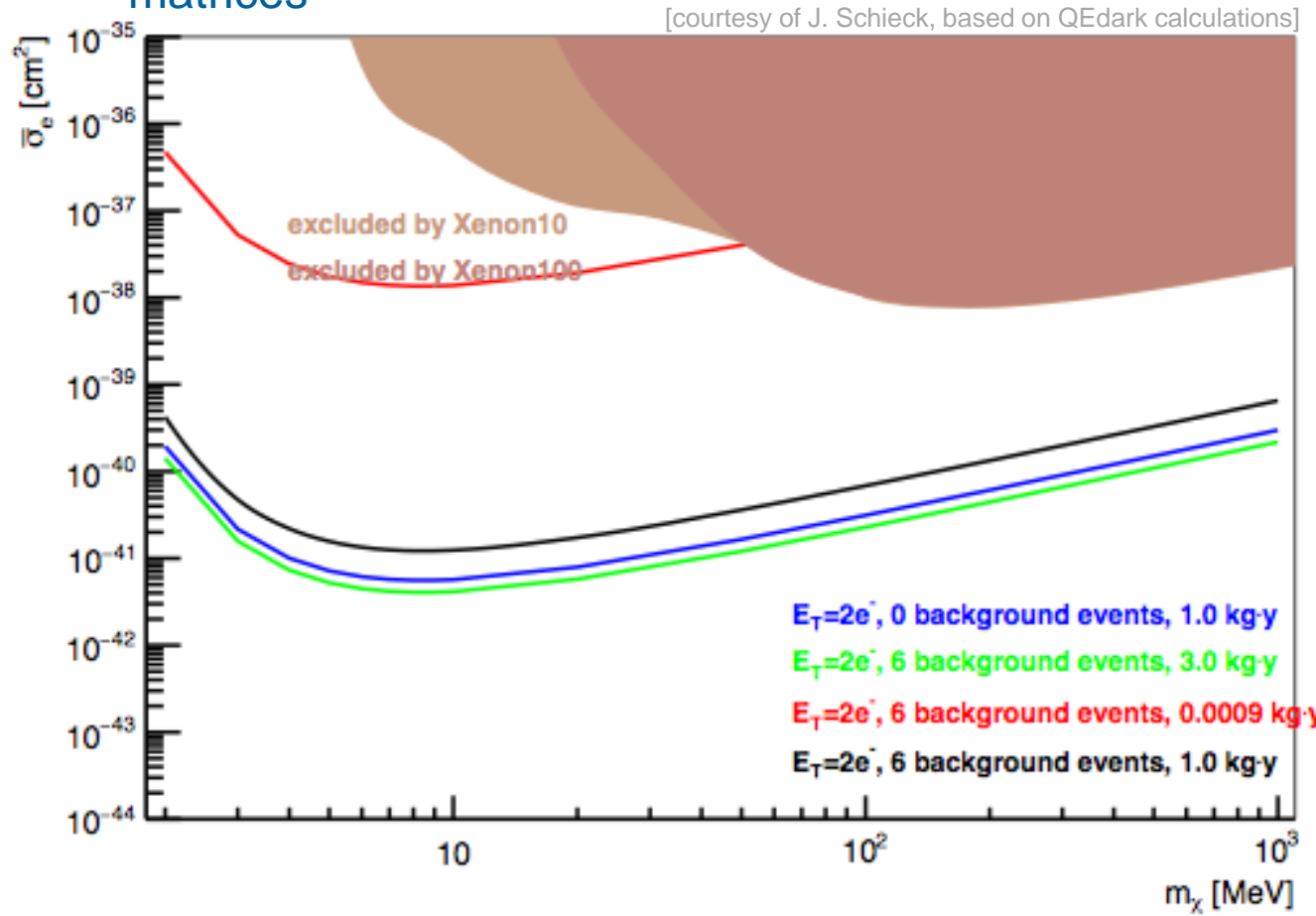


[courtesy of J. Treis]

- Expect preliminary results from the prototype setup (24 mg sensitive volume) in late 2019
- Physics run with significant result requires more matrices



[courtesy of J. Treis]



Initial goal: 0.9 g.yr

→ 40 matrices à 24mg

→ ~1g sensibles volume

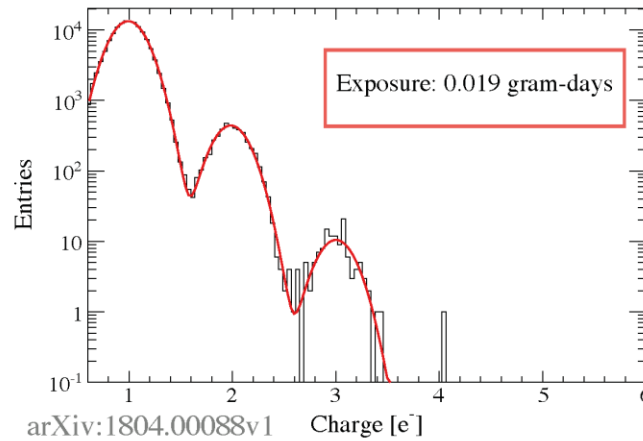
Summary

- **Sub-GeV/c²** dark matter is a **attractive alternative** to classic WIMPs
- Potential signature: **electron scattering**
- Require semiconductor detectors with **sub-e⁻ RMS noise level**
- **DEPFET-RNDR successfully demonstrate** such a low noise level
- **DANAÉ** is a new project aiming to **utilizing DEPFET-RNDR to search for sub-GeV/c² dark matter** interactions in silicon
- Under construction: **DANAÉ prototype** with 64pixel x 64pixel detector matrix
- Expect **first test-of-principle** measurement in **late 2019**

→ **Stay tuned** for future results!

Additional slides

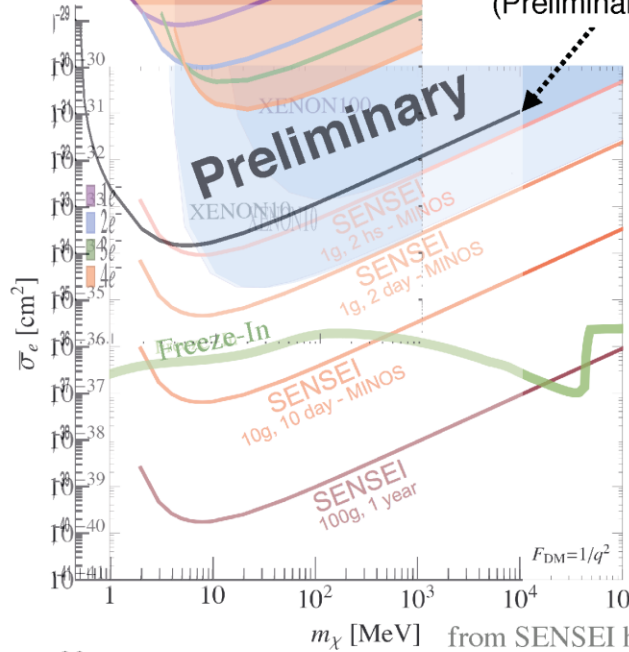
Expected 1day exposure compared to SENSEI



SENSEI prototype physics run

DANAЕ prototype 24 mg one-day exposure zero background expected reach (Preliminary)

DM-electron cross section



[courtesy of H. Shi (ICHEP2018)]

A comparison with skipper CCD

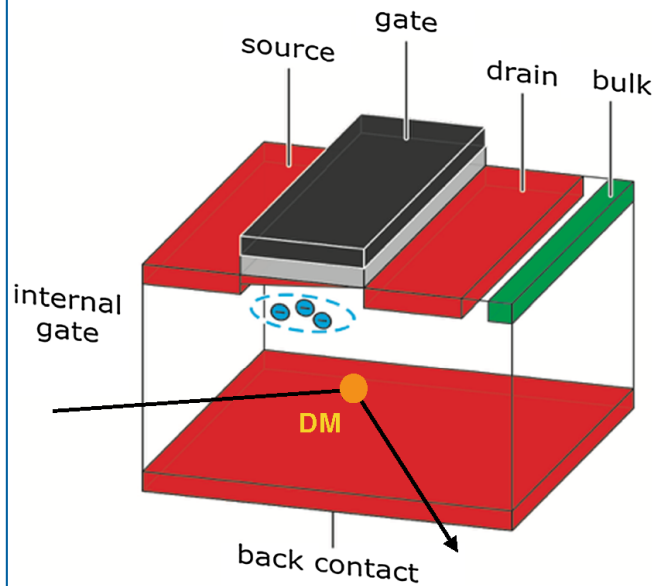
Type	Pixel format [μm]	prototype mass	operating temp	dark current	readout time (1sample)	readout noise (optimal)
skipper CCD	15 x 15 x 200	0.071 g	140 K	$\leq \sim 1.14$ <u>e-/pix/day</u>	10 μs/pix/ amplifier	0.068 e-rms/pix
RNDR DEPFET	75 x 75 x 450	0.024 g	≈ 200 K	≤ 1 <u>e-/pix/day</u>	4 μs/ 64 pix	0.2 e-rms/pix

similar concepts of non-destructive readout, compatible performance;
 different architecture, different systematics;
 -> good complementary from experimental point of view

DEPFET with RNDR

RNDR : repetitive non-destructive readout

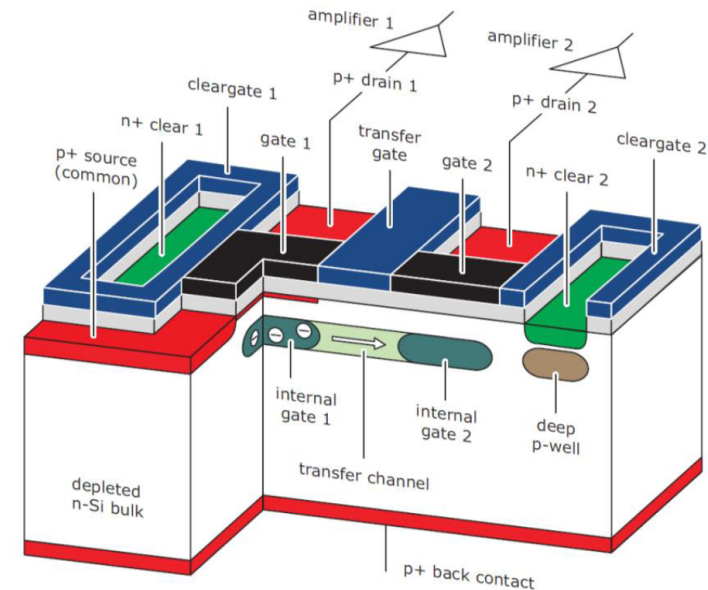
structure of a basic DEPFET cell :
a “subpixel”



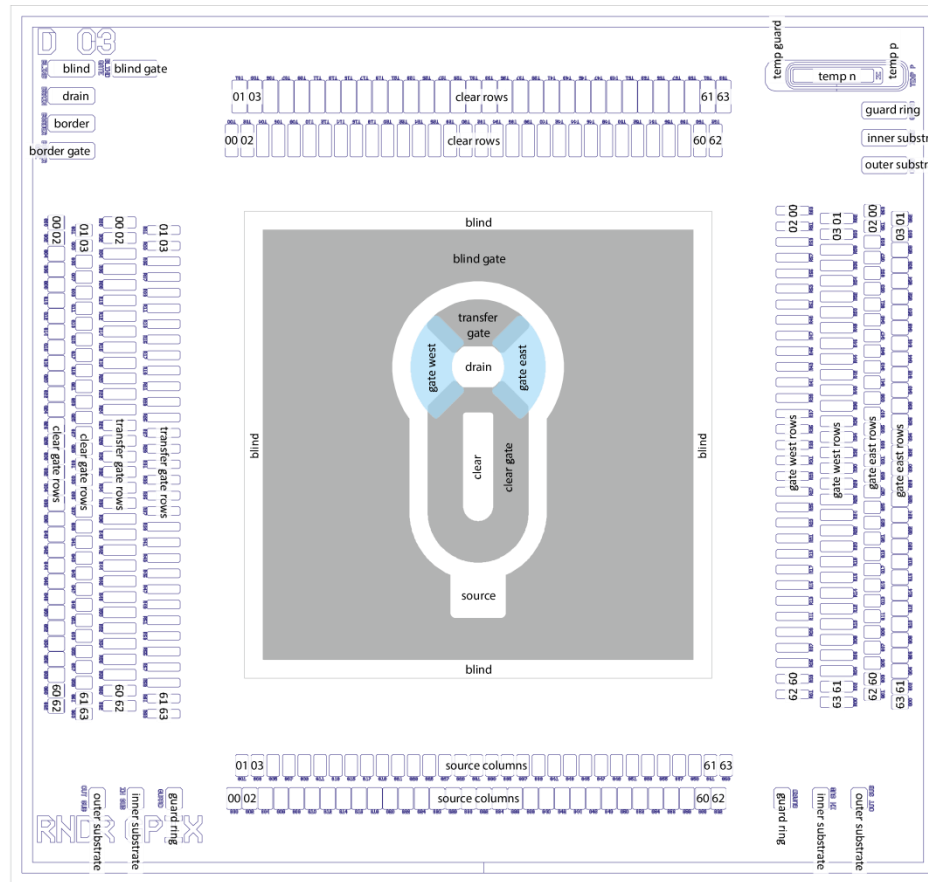
EPJ C, 77(12), 279 (2017)

fully-depleted n-Si

structure of RNDR DEPFET “super-pixel”



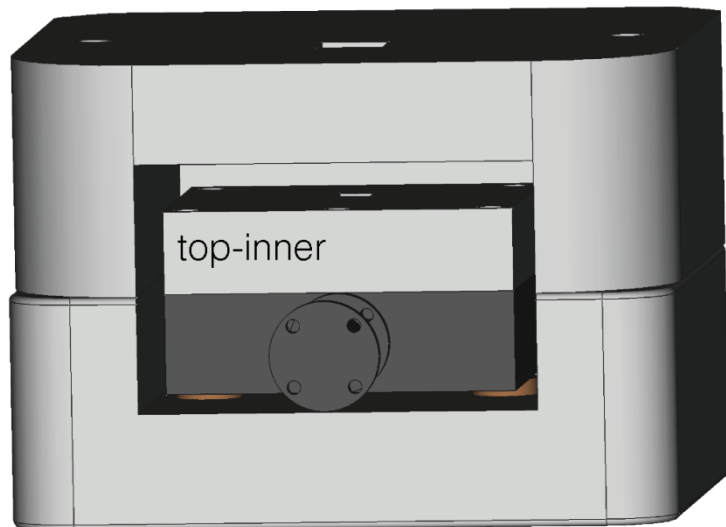
EPJ C, 77(12), 279 (2017)



compact RNDR & blind structure name RNDR_GPIX
 chip size 8.5 x 8.0 mm²
 format 64 x 64
 pixel size 75 x 75 μm²
 PXD7 chip D.03

Cooling & shielding layout

top-out



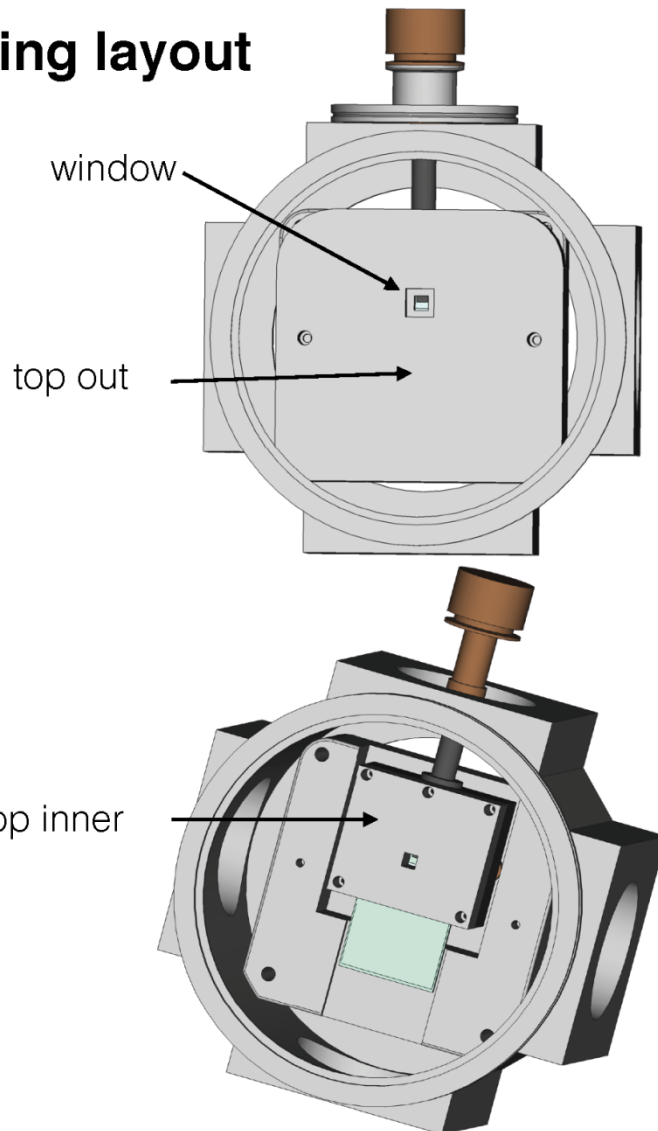
bot-out

outer shielding : support structure
inner shielding : cooling contact

window

top out

top inner



DEPFET matrix control & readout electronics

Detector matrix

Front-end ASICS for the 64x64 matrix with interface to Switcher-S, VERITAS

Switcher-S

64x2 channel analog multiplexer

Readout board

switcher id	W	N	E
function	Gate 1 & 2	Gate common	clear & transfer gate
Voltage [V]	-2.5 ~ + 5	-0.5 ~ +20	-0.5 ~ + 20/25

VERITAS

- VERITAS 2.1 ASIC in the AMS 0.35 μm CMOS 3.3 V technology
- 64 analog readout channels able to process in parallel the **signals coming from 64 DEPFET devices**.

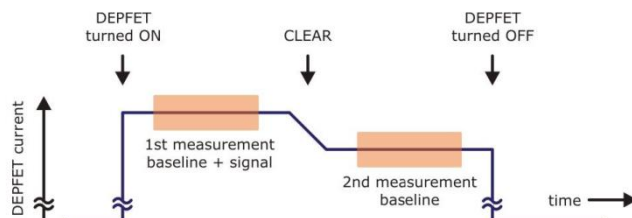
ADC

FADC type digitizer



Detector Structures – Matrix Devices

readout sequence

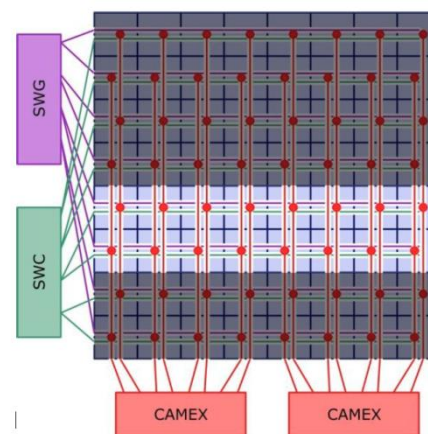


Correlated double sampling:

- 1st measurement: signal + baseline
- clear: removal of signal charges
- 2nd measurement: baseline

difference = signal
complete clear is mandatory!

matrix operation



vertical signal lines
1 active row, other pixels integrating

option to speed up (1)

- readout parallelisation
- 2 x readout channels, 2 active rows